

SPIN CALORICS AND SPIN TRANSFER IN MAGNETIC NANOSTRUCTURES

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Collaborations:

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DFG
Priority
Programme
SpinCat



FAQ's: Where is Bielefeld ?

There



Introduction

Spincalorics

Spincalorics

Spin Transfer

New Materials

Spintransfer

**LSSE in Ni-Ferrite
TSSE in Permalloy ??**

in MTJs

in MTJs

in p-MTJs

STT at the limit

High K , low M_s

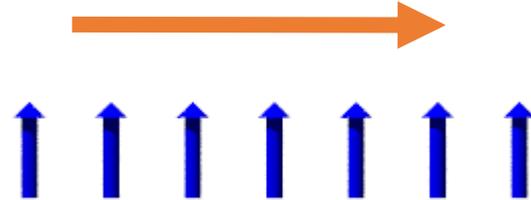
There are many ways to transfer spins / angular momentum:

charge & angular momentum



by a spin polarized current

angular momentum



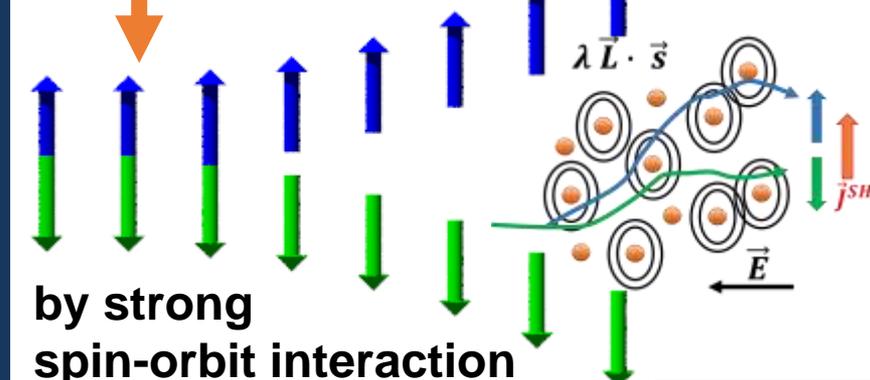
by Stoner-like spin flips

angular momentum



by a temperature grad.

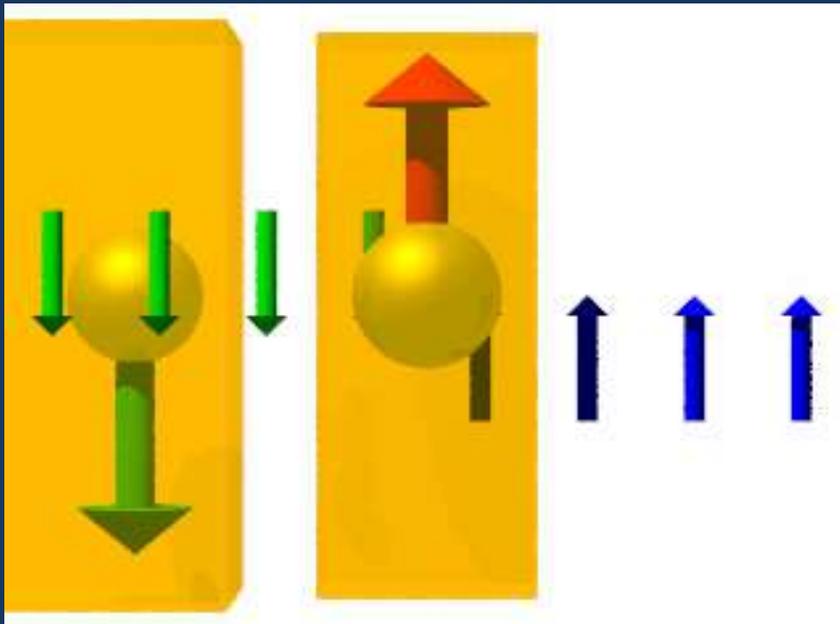
charge & angular momentum
but \perp



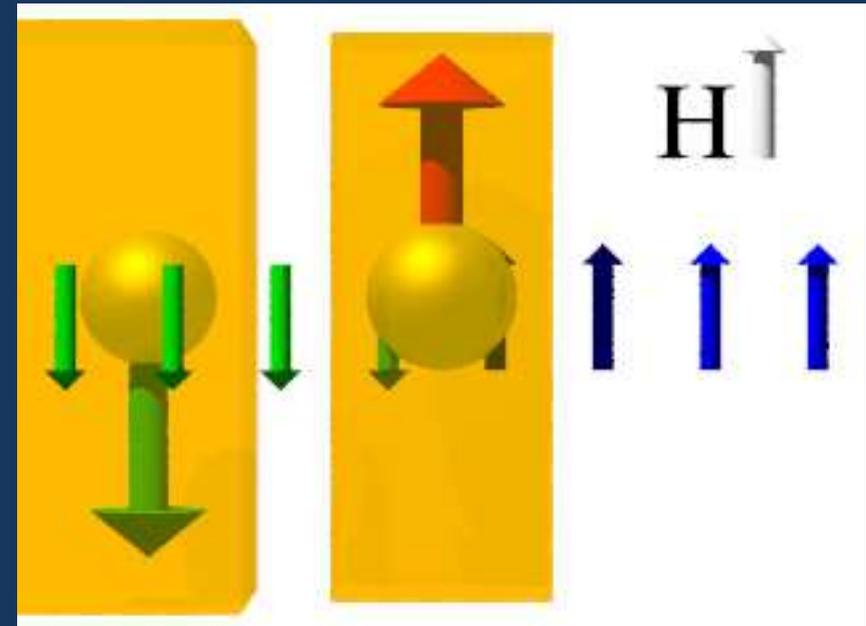
by strong
spin-orbit interaction

... but why should one like to transfer spins / angular momentum?

- Because the total angular momentum is conserved
- Spintransfer gives handle on magnetization



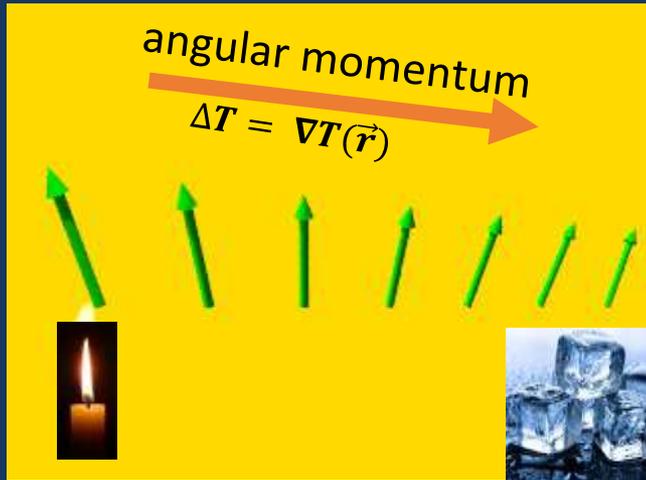
Example 1: Spin-Transfer-Torque Switching (STT) of a magnetic double layer
→ writing information



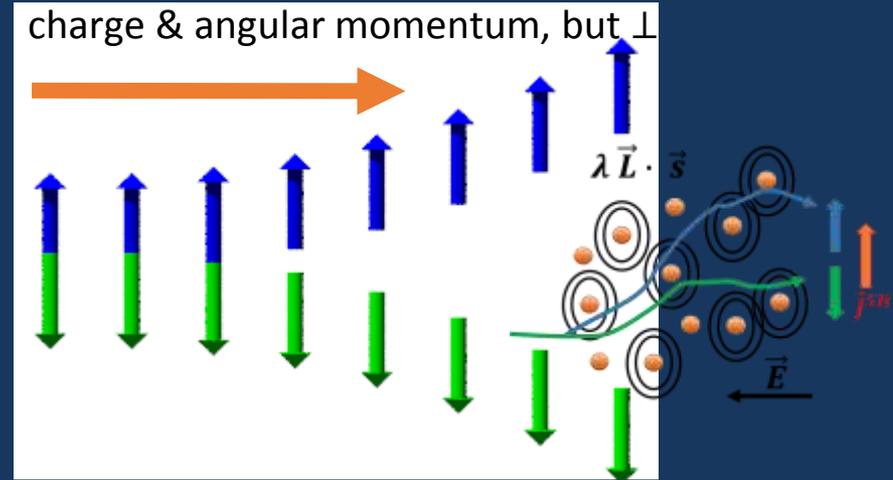
Example 2: Spin-Transfer-Torque induced magnetization oscillations in a magnetic double layer
→ creating microwave emission

.. and many more (driving magnetic domain walls, enhancing their speed, ..)

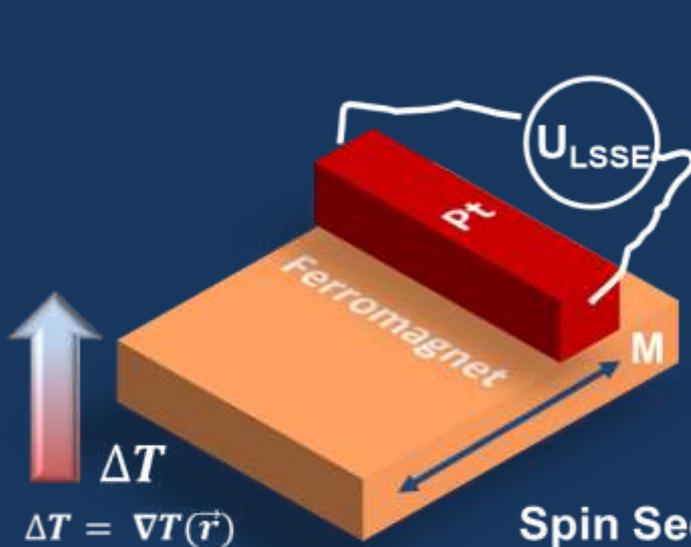
Spincalorics – Seebeck and Inverse Spin Hall Effect



Spintransport by a T-gradient

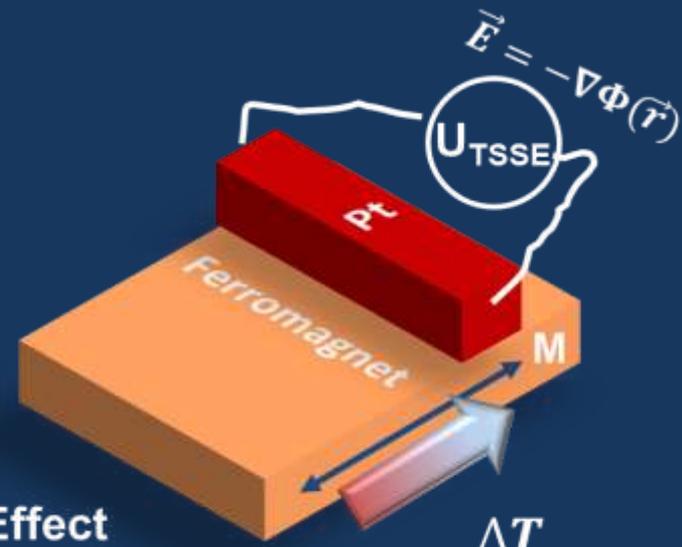


Spin separation in Spin Hall Effect



Spin Seebeck Effect

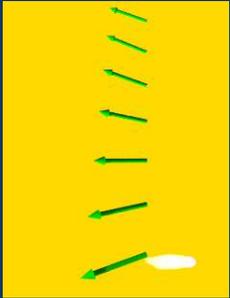
Longitudinal



Transverse (???)

Spincalorics – Seebeck and Inverse Spin Hall Effect

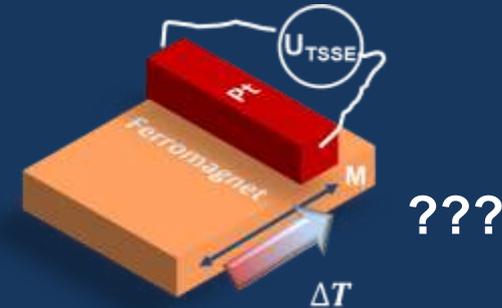
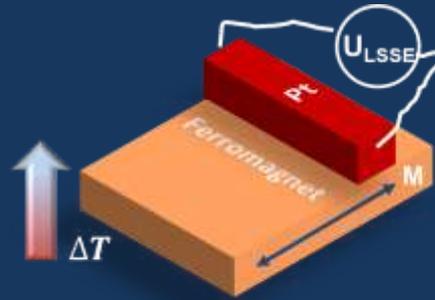
Ingredients for SpinCalorics:



Induced Spin Current:

$$\vec{J}_S \parallel \nabla T$$

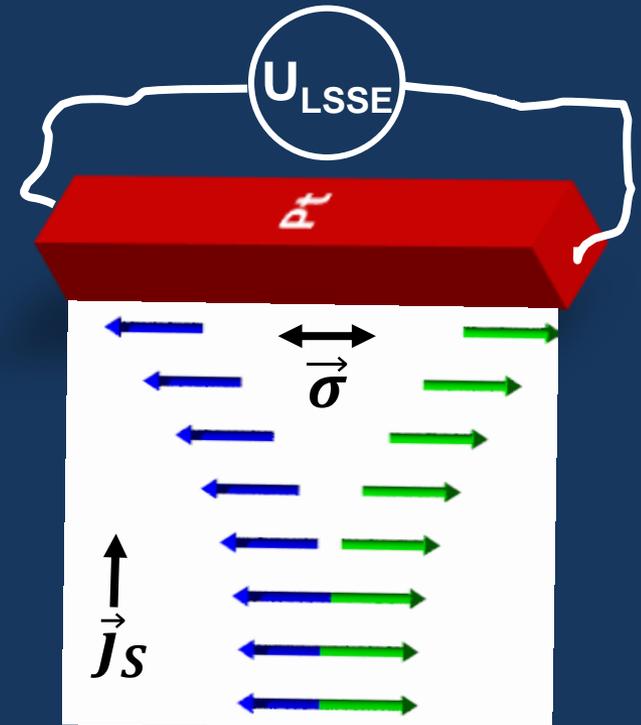
$$\vec{\sigma} \parallel \vec{M}$$



Voltage V induced by the Inverse Spin Hall Effect:

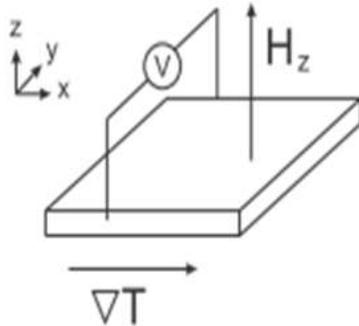
$$\vec{E}_{ISHE} \propto \vec{J}_S \times \vec{\sigma}$$

$\vec{\sigma}$: Spin polarization of charge carriers

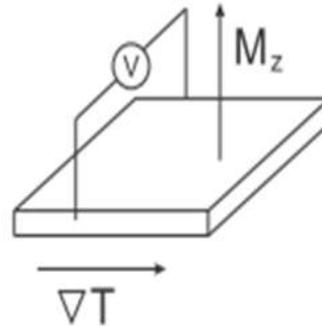


Nernst effects

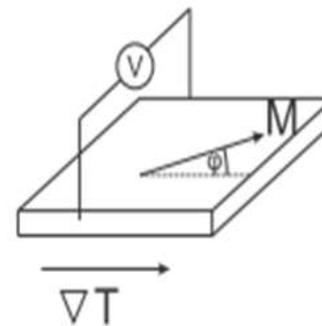
Nernst effect: $V \propto H_z$



anomalous
Nernst effect: $V \propto M_z$



planar
Nernst effect: $V \propto M^2 \sin(2\phi) \propto M_x \cdot M_y$



$$\vec{E}_{NE} \propto \nabla T \times \vec{H}$$

$$\vec{E}_{ANE} = \alpha \nabla T \times \vec{m}.$$

Nernst effects only in
conducting materials

Overview of Spin-Seebeck- and competing Nernst-Effects:

		Grad _x T				Grad _z T			
		Nernst ∝ Hz	anomalous Nernst ∝ Mz	planar Nernst ∝ Mx ² My	transversal spin-Seebeck ∝ sigma _{max}	Nernst ∝ Hx	anomalous Nernst ∝ Mx	planar Nernst ∝ My ² Mz	longitudinal spin-Seebeck ∝ sigma _{max}
Hx	NiFe								
	Pt								
Hy	NiFe								
	Pt								
Hz	NiFe								
	Pt								
Hx,Hy	NiFe								
	Pt								
Hy,Hz	NiFe								
	Pt								
Hz,Hx	NiFe								
	Pt								
Hx	NiFe2O4								
	Pt								
Hy	NiFe2O4								
	Pt								
Hz	NiFe2O4								
	Pt								
Hx,Hy	NiFe2O4								
	Pt								
Hy,Hz	NiFe2O4								
	Pt								
Hz,Hx	NiFe2O4								
	Pt								

no effect
 linear
 anisotropy
 hysteresis

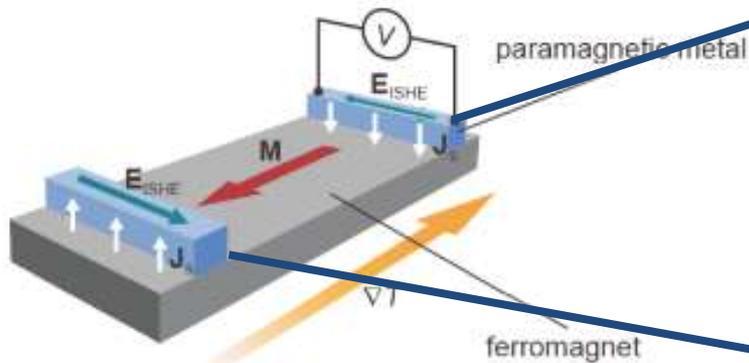


put together
by



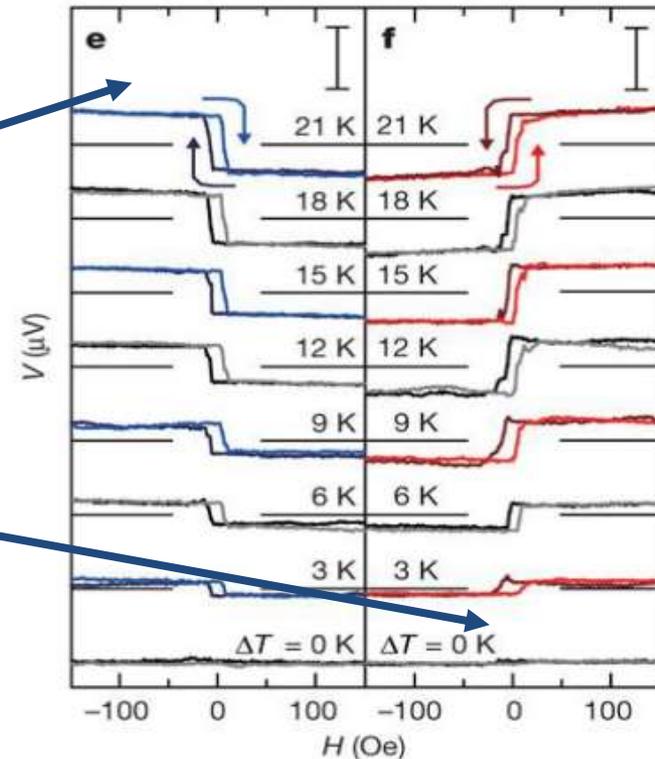
**Timo
Kuschel**

Transverse Spin-Seebeck-Effects was the first to be reported:



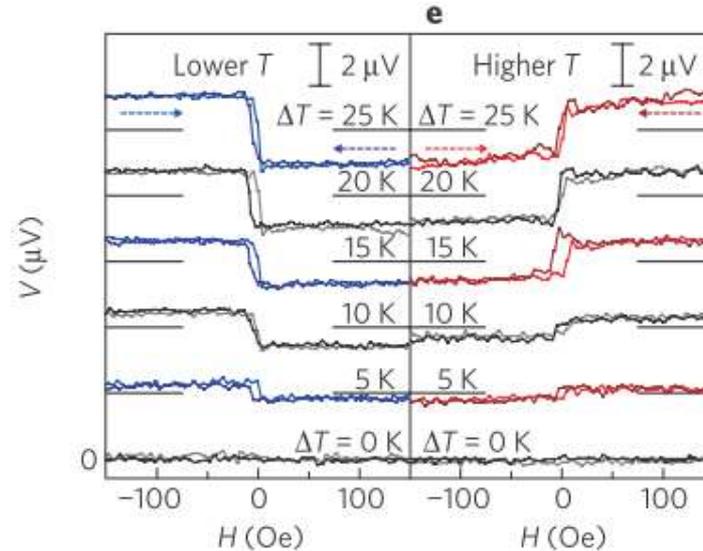
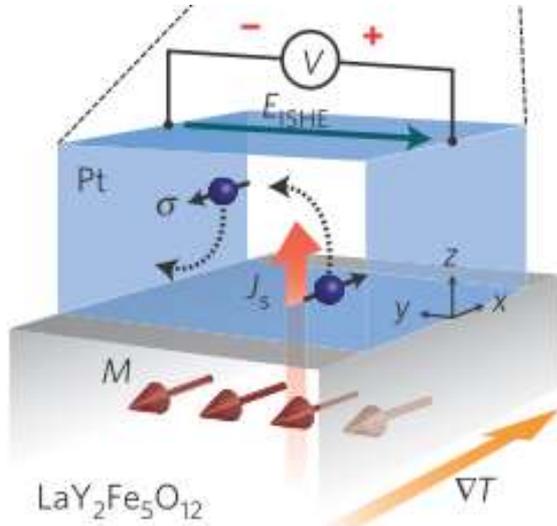
■ $E_{ISHE} \propto J_s \times \sigma$

■ K. Uchida et al., Nature **455**, 778 (2008)

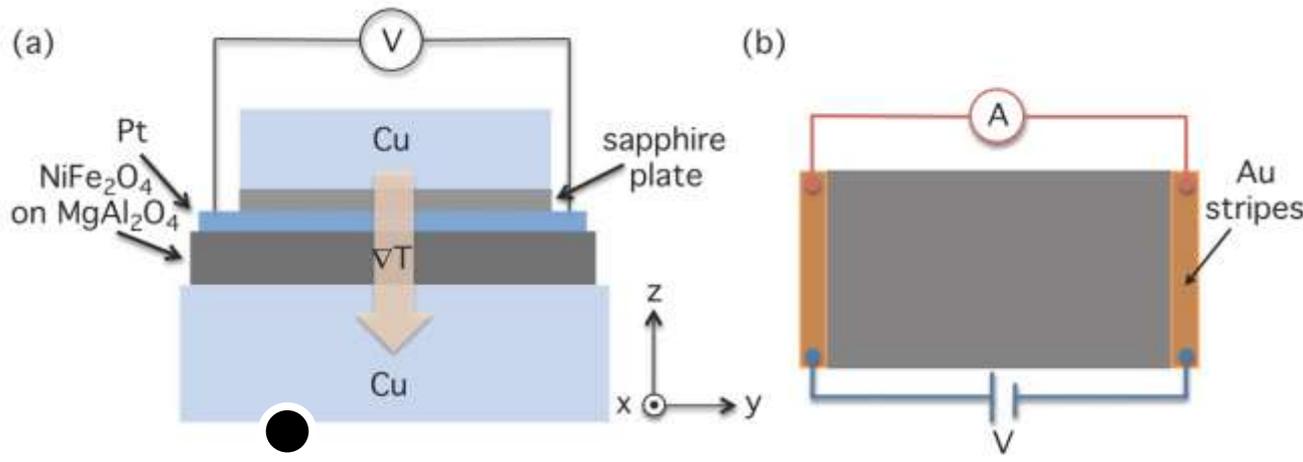


TSSE still under discussion ..

Other Spin-Seebeck-Effects :



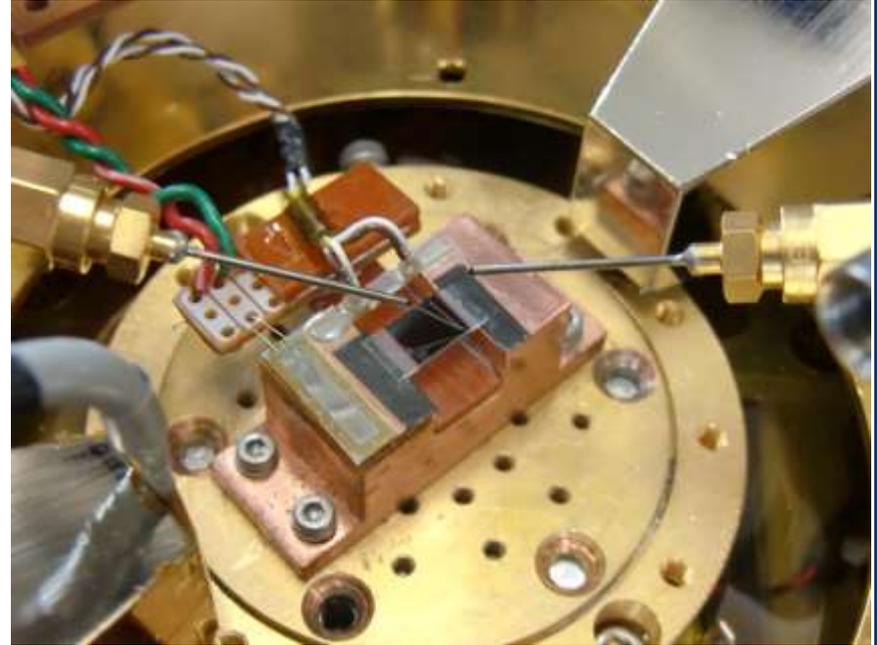
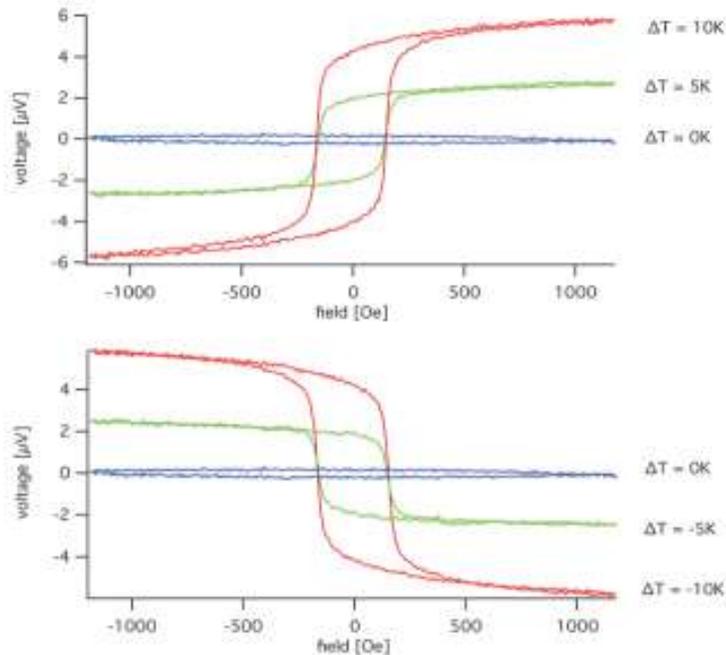
On insulating
 $\text{LaY}_2\text{Fe}_5\text{O}_{12}$
Uchida et.al.,
Nat. Mat.
Sept. 2010



Sample
arrangement for
LSSE (left) and
conductivity (right)
@Bielefeld

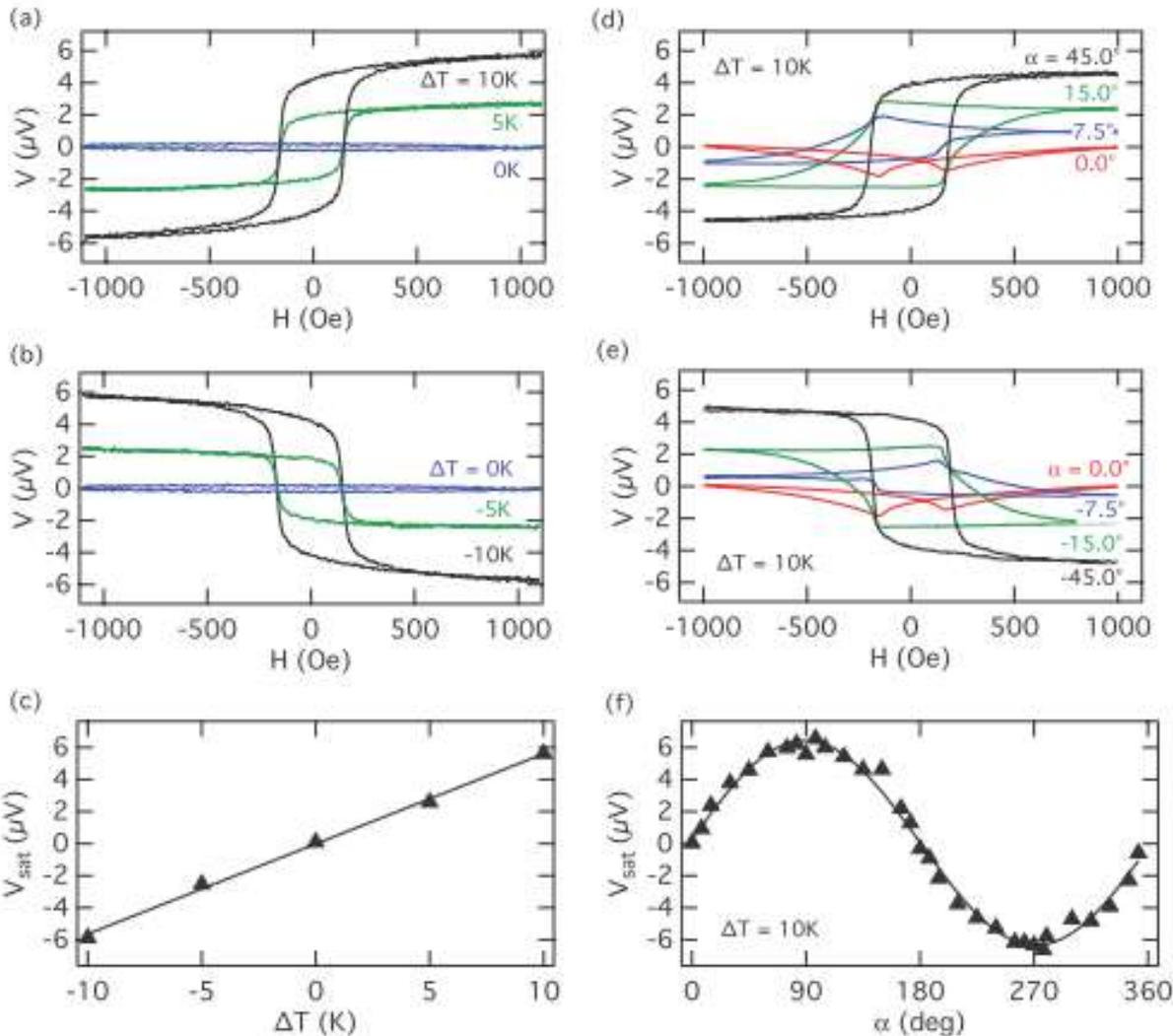
T_0 : variable base temperature

NFO (deposition time: 100 min.) on MAD



Measured in Prof. Saitoh's lab,
Tohoku University, Sendai, Japan
(T. Kuschel, D. Meier)
 NiFe_2O_4 from A. Gupta, Alabama
University, Tuscaloosa, USA



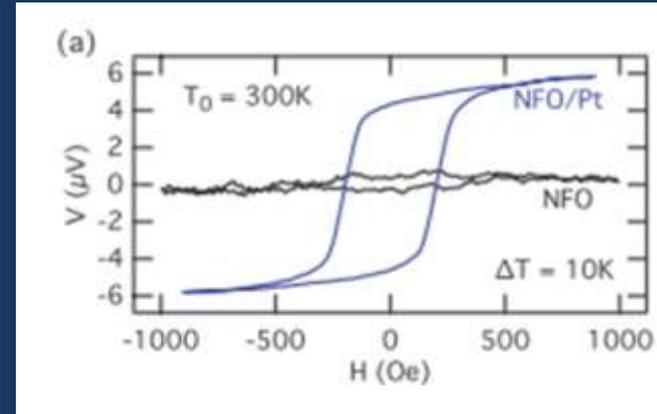
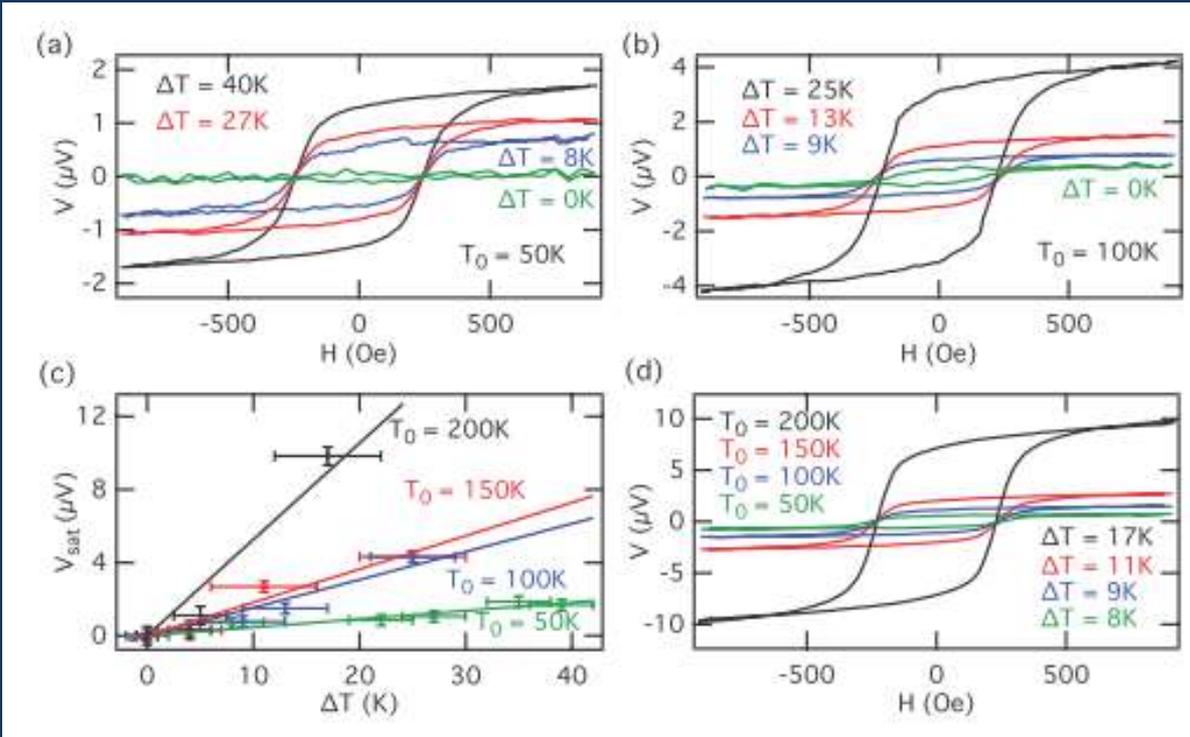


Measured @Bielefeld lab,
CVD-NiFe₂O₄ from A. Gupta, Alabama
PVD-NiFe₂O₄ from Bielefeld-lab

.. reproducible signals

but
watch Nernst effects!

a, b, d, e: LSSE in NiFe₂O₄ for various values of ΔT and angle α between ΔT and \vec{H}
c, f: LSSE amplitude as function of ΔT and α



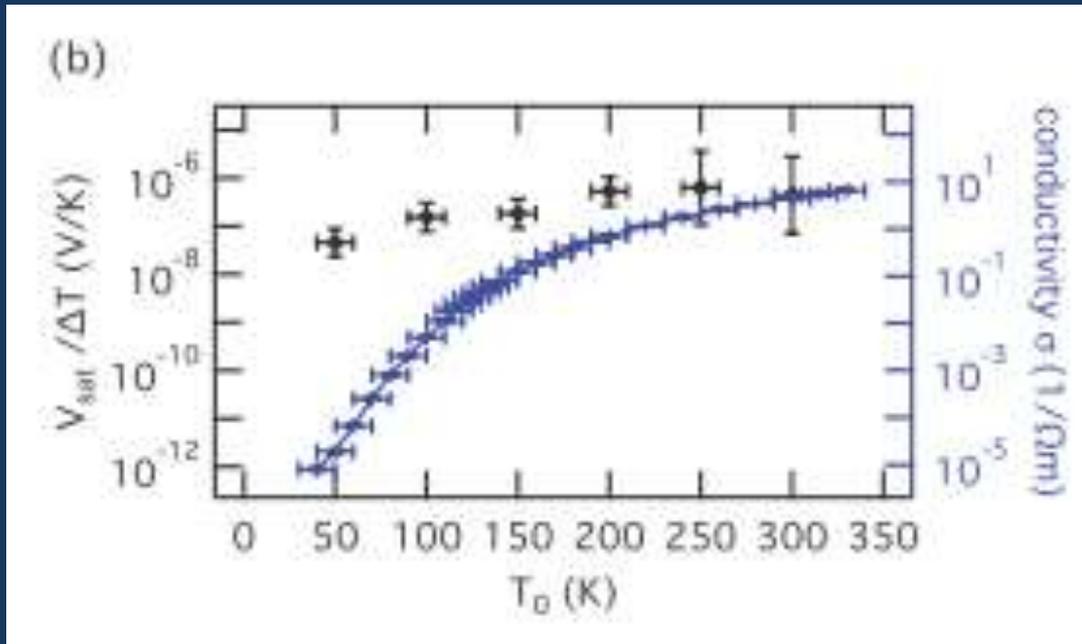
LSSE on Pt-stripe and Anomalous Nernst signal on bare NiFe_2O_4

a, b, d: LSSE in NiFe_2O_4 films for various values of ΔT and T_0
c: LSSE amplitude vs ΔT for various T_0

→ use semiconducting properties of NiFe_2O_4 and variable base temperature

NiFe_2O_4 has semiconducting-type temperature dependence of the conductivity

→ compare LSSE at variable base temperature with conductivity



→ Conductivity drops by 6 orders of magnitude,
→ V_{sat} of (??) LSSE drops only by 1 ½ orders

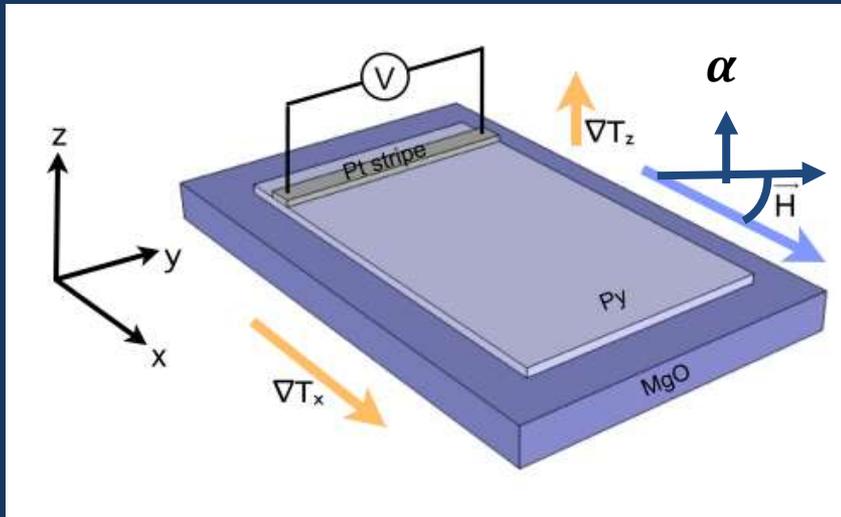
→ V_{sat} due to LSSE

→ directly measured Nernst effect agrees with these data

PHYSICAL REVIEW B 87, 054421 (2013)

Thermally driven spin and charge currents in thin $\text{NiFe}_2\text{O}_4/\text{Pt}$ films

D. Meier,^{1,*} T. Kuschel,¹ L. Shen,² A. Gupta,² T. Kikkawa,³ K. Uchida,^{3,4} E. Saitoh,^{3,5,6,7} J.-M. Schmalhorst,¹ and G. Reiss¹



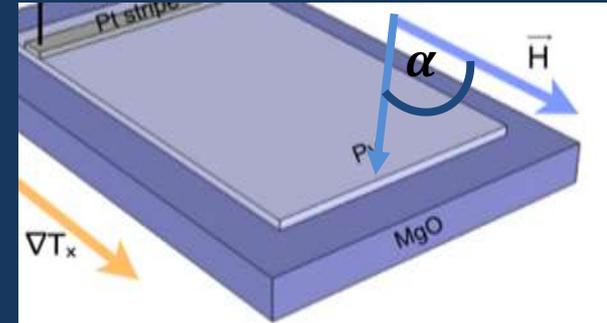
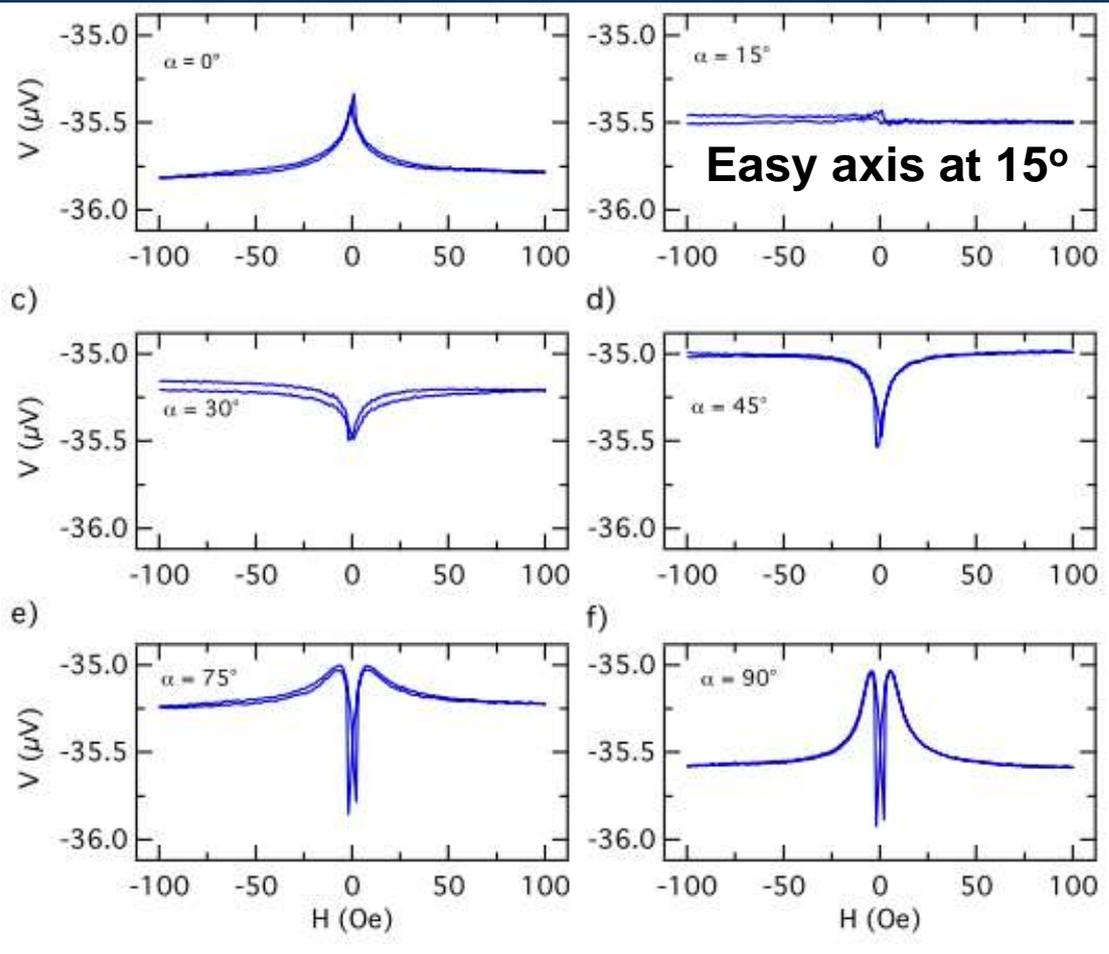
Experimental arrangement (new setup) with

- Two possible temperature gradients
- Wire bonding to Pt
- In vacuum
- At variable base temperature

Expect: ANE for ∇T_z : $\vec{E}_{ANE} = N_{ANE} \nabla T \times \vec{M}$.

Expect: PNE for ∇T_x : $V_y \propto |M|^2 \sin(\varphi) \cos(\varphi) |\nabla T| \propto M_x \cdot M_y |\nabla T|$

? TSSE

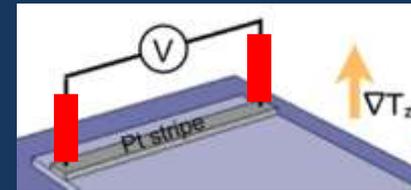
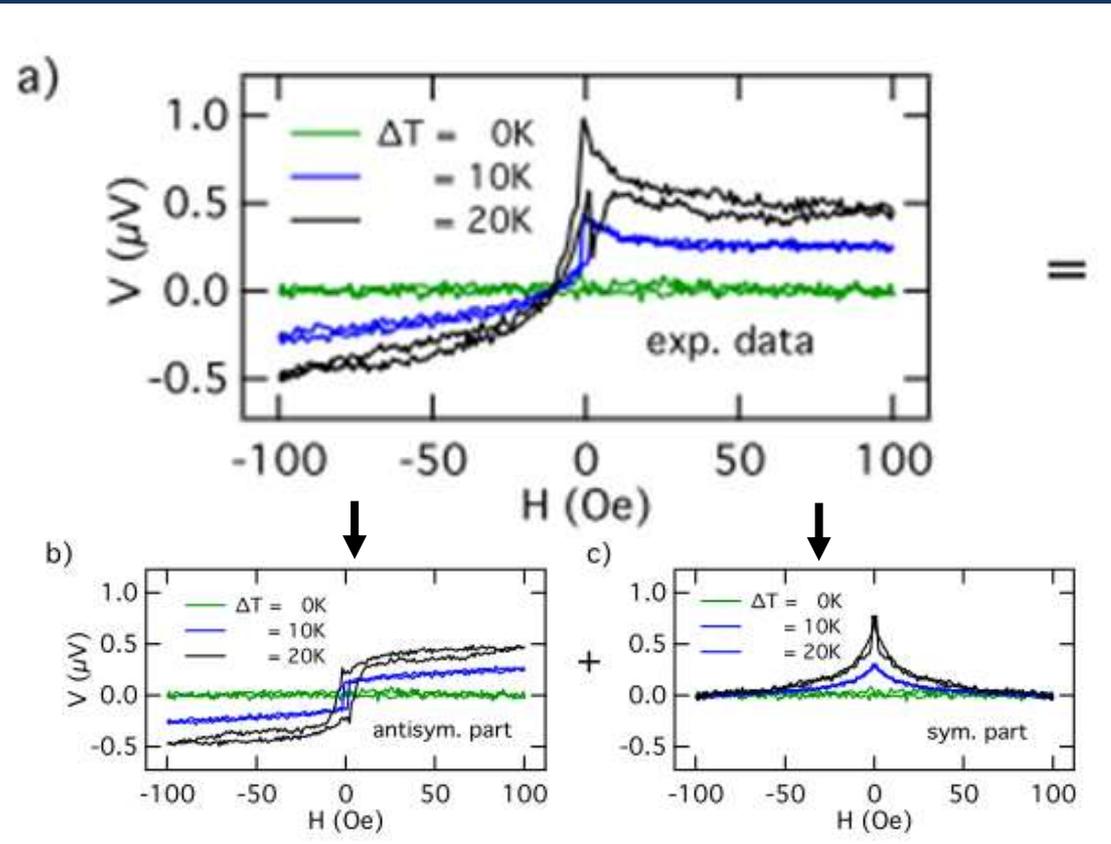


At $T_0 = 300\text{K}$
Pt-stripe on hot side of the sample.
Field in sample plane.
Thin W-tips as voltage probes

„TSSE“-signal for various values of α as a function of the external field H

→ only symmetric effects

Gives only PNE
(Planar Nernst Effect)



$T_0 = 300\text{K}$, ΔT variable
Pt stripe on hot side
of the sample,
thick Au tips as voltage
probes (1mm)

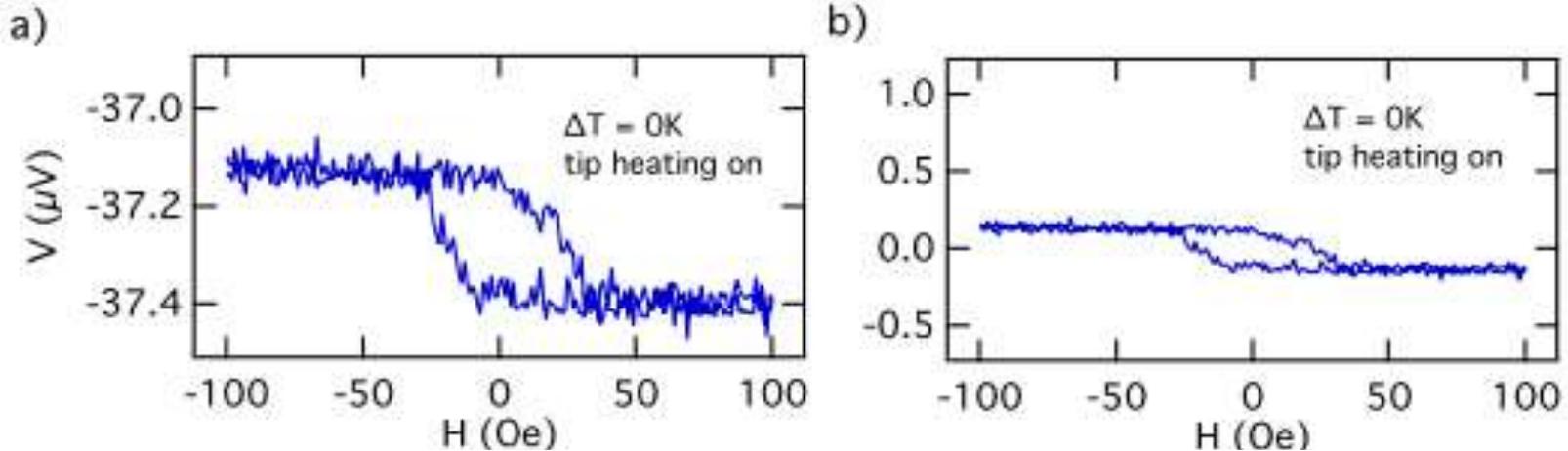
**Symmetric part:
Planar Nernst Effect**

**Antisymmetric:
Anomalous Nernst
Effect due to heat
transport by Au-tips**

a) „TSSE“ signal on Pt on Py for various ΔT as a function of the external field H measured with thick Au-tips

b, c: antisymmetric and symmetric part of the measured signal

→ Heat tips and look at voltage signals in TSSE-geometry!



PHYSICAL REVIEW B **88**, 184425 (2013)



Influence of heat flow directions on Nernst effects in Py/Pt bilayers

D. Meier,^{1,*} D. Reinhardt,¹ M. Schmid,² C. H. Back,² J.-M. Schmalhorst,¹ T. Kuschel,¹ and G. Reiss¹

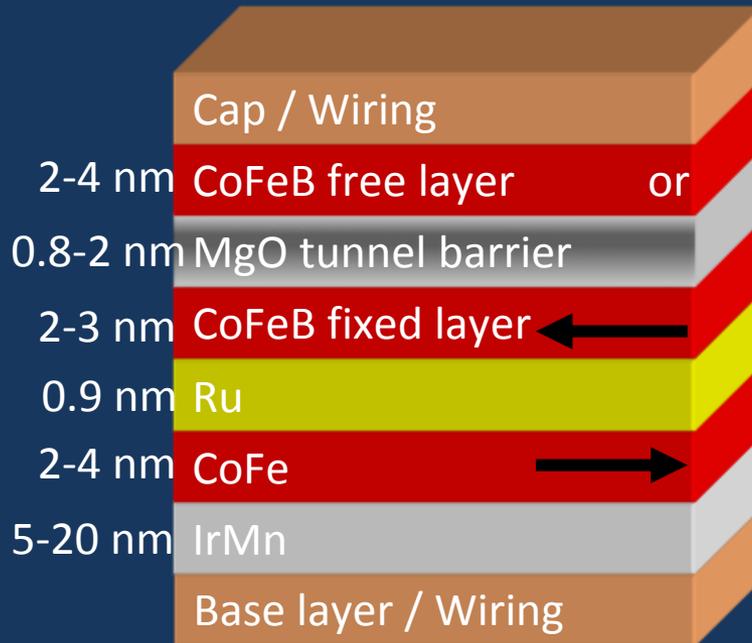
PRL **111**, 187201 (2013)

PHYSICAL REVIEW LETTERS

week ending
1 NOVEMBER 2013

Transverse Spin Seebeck Effect versus Anomalous and Planar Nernst Effects in Permalloy Thin Films

M. Schmid,¹ S. Srichandan,¹ D. Meier,² T. Kuschel,² J.-M. Schmalhorst,² M. Vogel,¹ G. Reiss,²
C. Strunk,¹ and C. H. Back¹

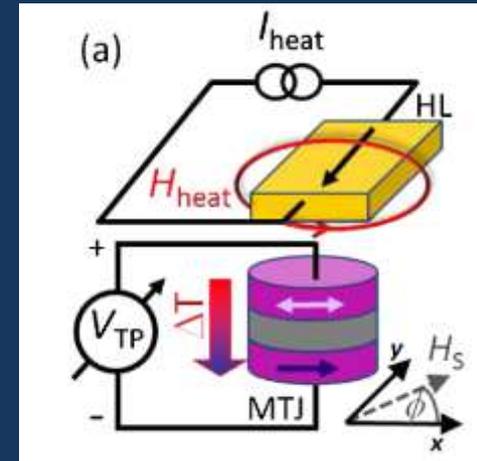


MTJ Stack

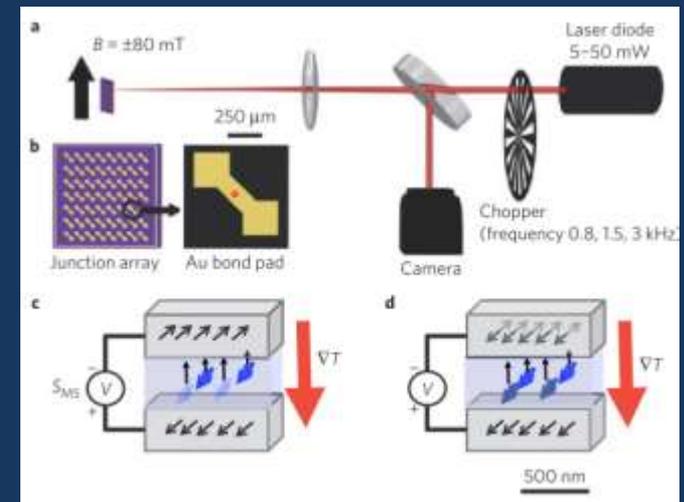
Magnetic Tunnel Junctions with CoFeB (in plane or perpendicular) and other materials

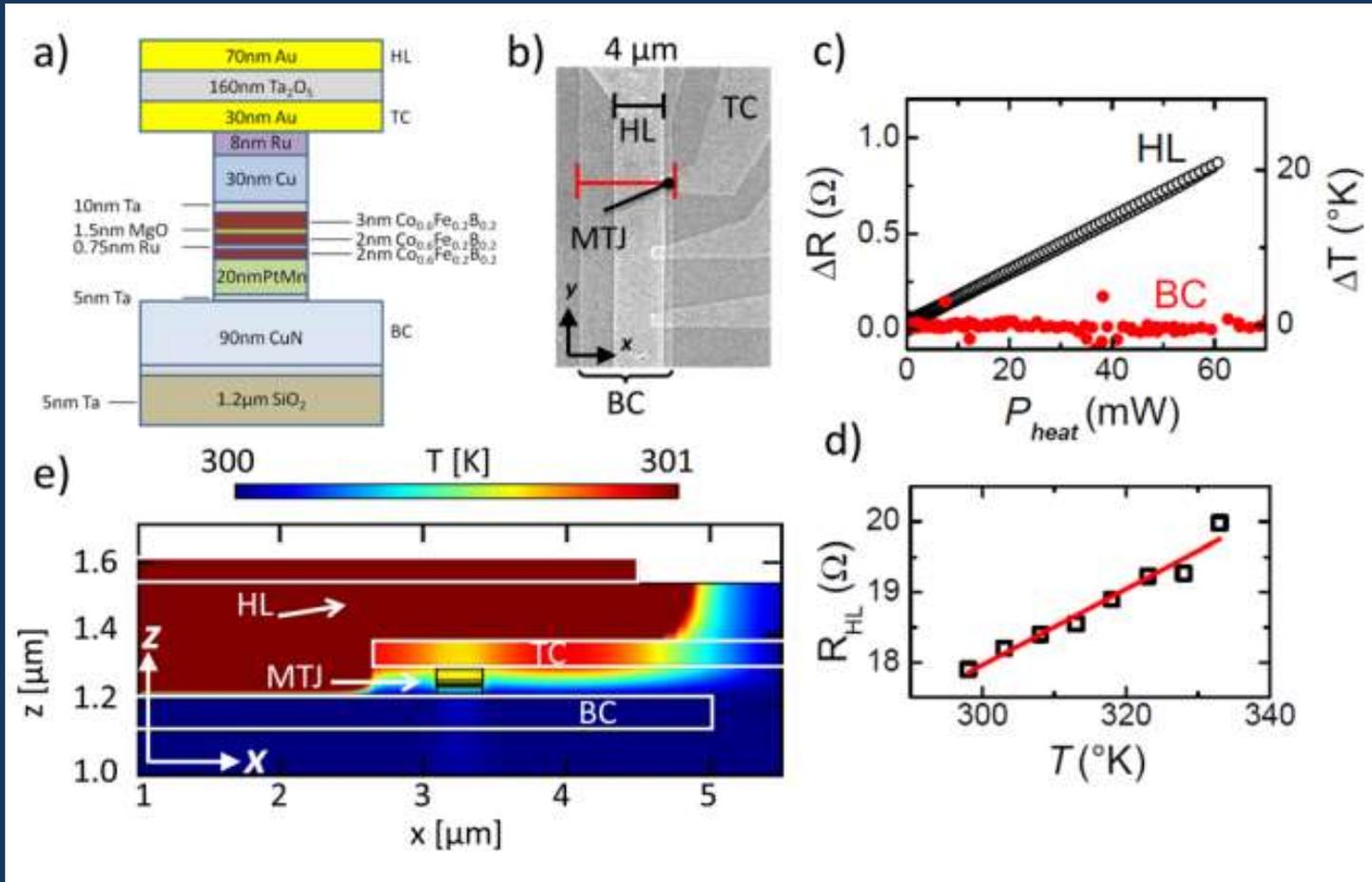


Heating by heater line

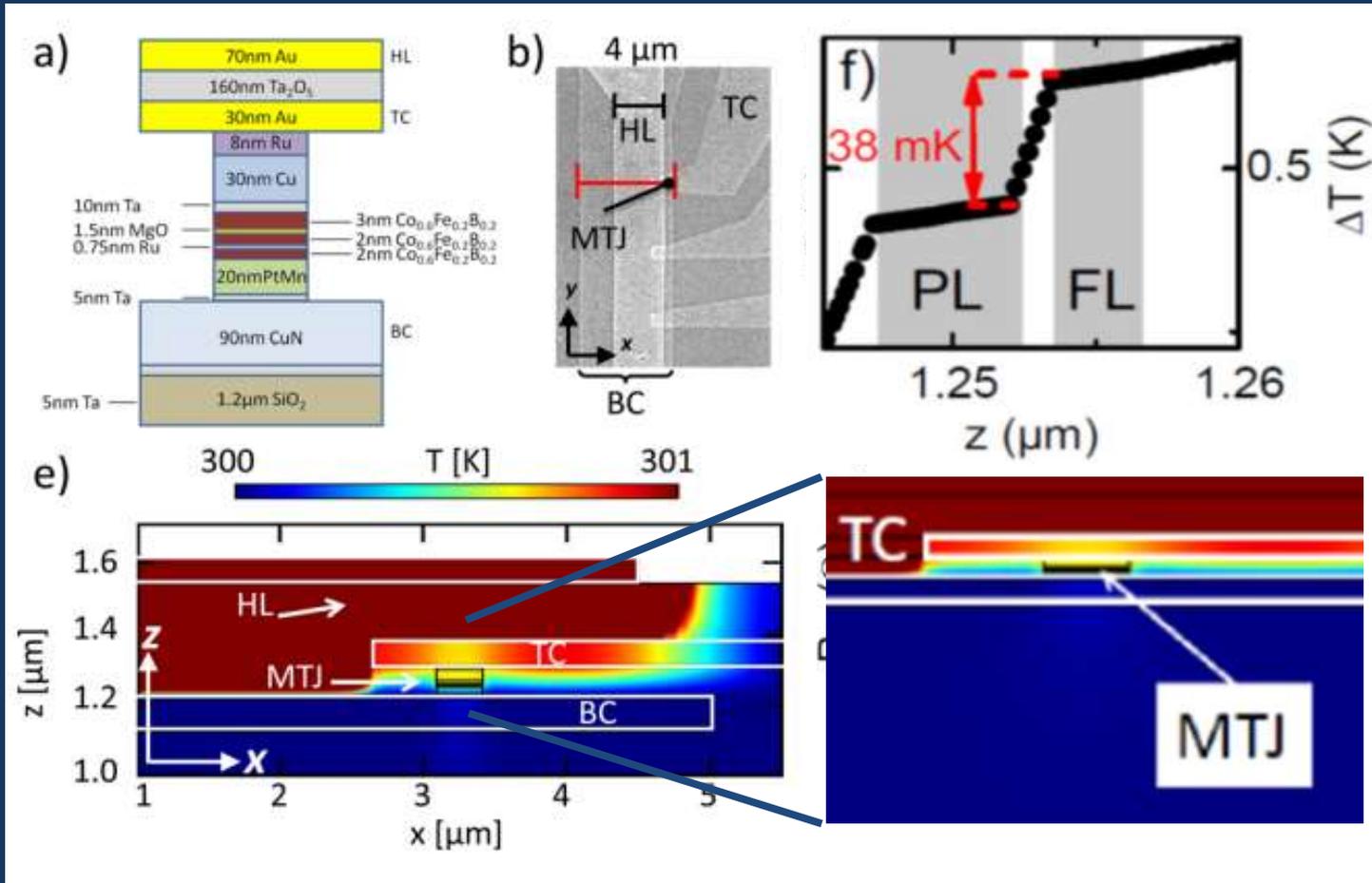


or laser pulses





(a) MTJ stack composition. HL, TC and BC: heater line, electrical top and contact
 (b) SEM image with HL, BC, and TC (MTJ nanopillar indicated). Red line: cross section for simulations. (c) Resistance increase of HL (open dots) and BC (full dots) vs heating power. Right : temperature increase of HL and BC. (d) Measured temperature dependence of HL resistance. (e) Simulated temperature distribution (2D cross section).

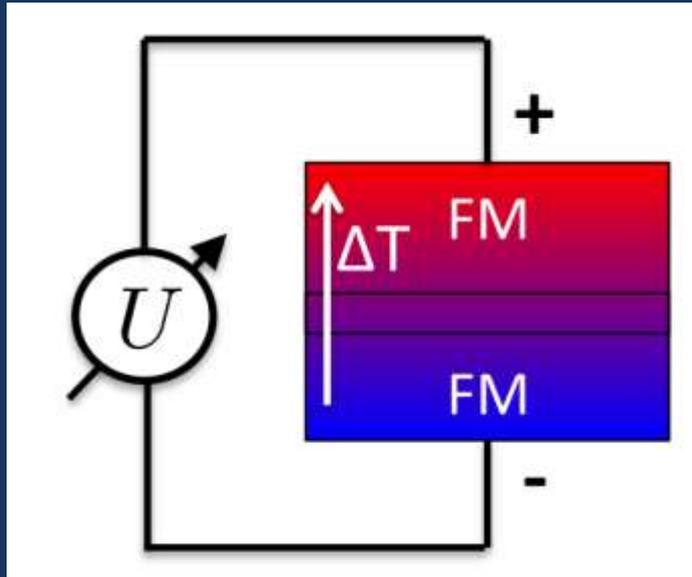


f) simulated temperature profile across the MgO barrier

and

enlarged view of the MTJ

(a) MTJ stack composition. HL, TC and BC: heater line, electrical top and contact
 (b) SEM image with HL, BC, and TC (MTJ nanopillar indicated). Red line: cross section for simulations. (c) Resistance increase of HL (open dots) and BC (full dots) vs heating power. Right : temperature increase of HL and BC. (d) Measured temperature dependence of HL resistance. (e) Simulated temperature distribution (2D cross section).

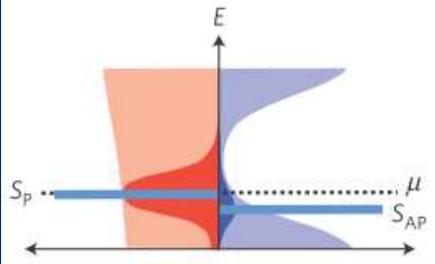


Seebeck coefficient **S** for tunnel junctions:

$$S = \frac{\int T(E)(E - \mu)(-\partial_E f(E, \mu, T))dE}{e T \int T(E)(-\partial_E f(E, \mu, T))dE}$$

$\partial_E f(E, \mu, T)$: Derivative of occupation function

High magneto-Seebeck effect

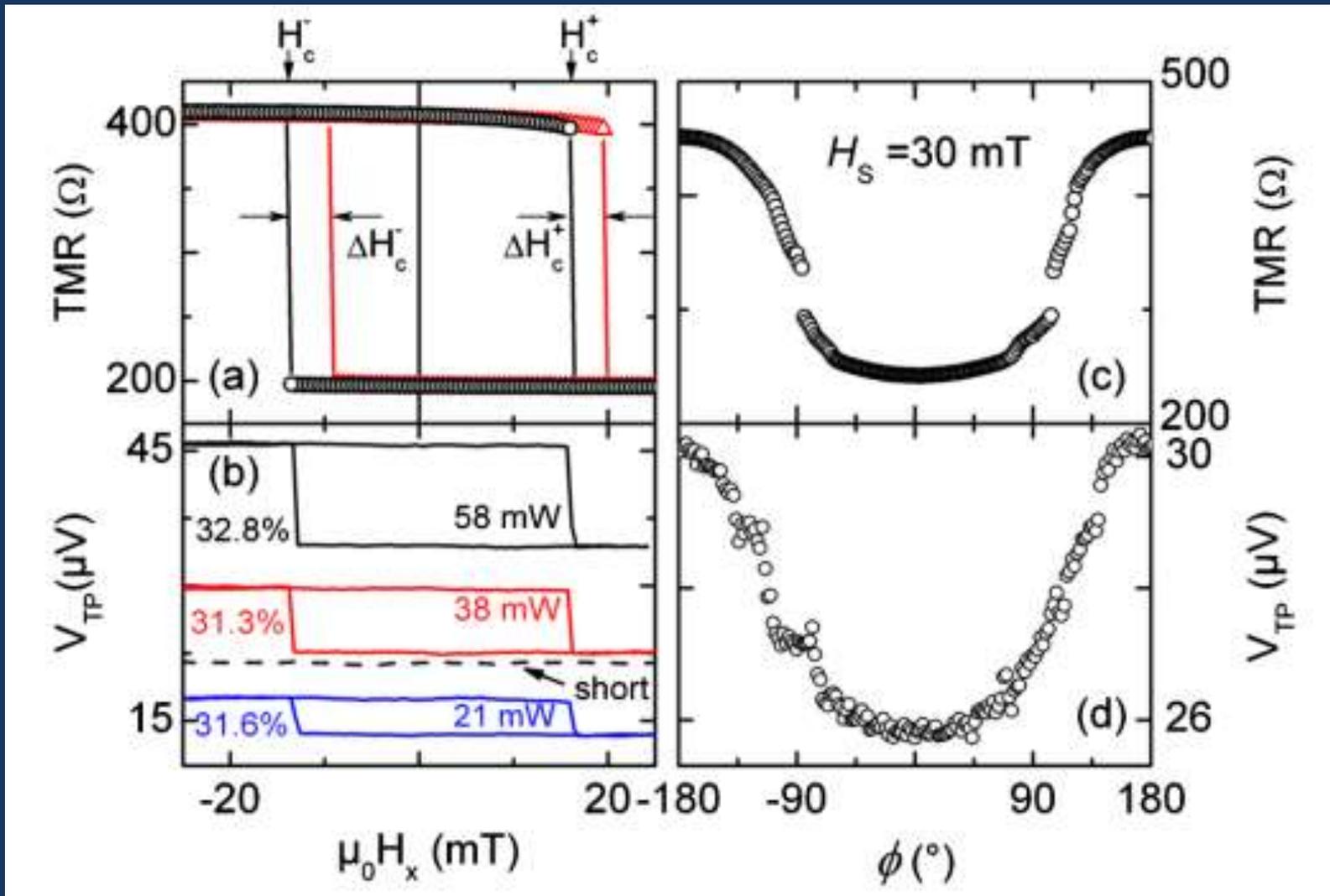


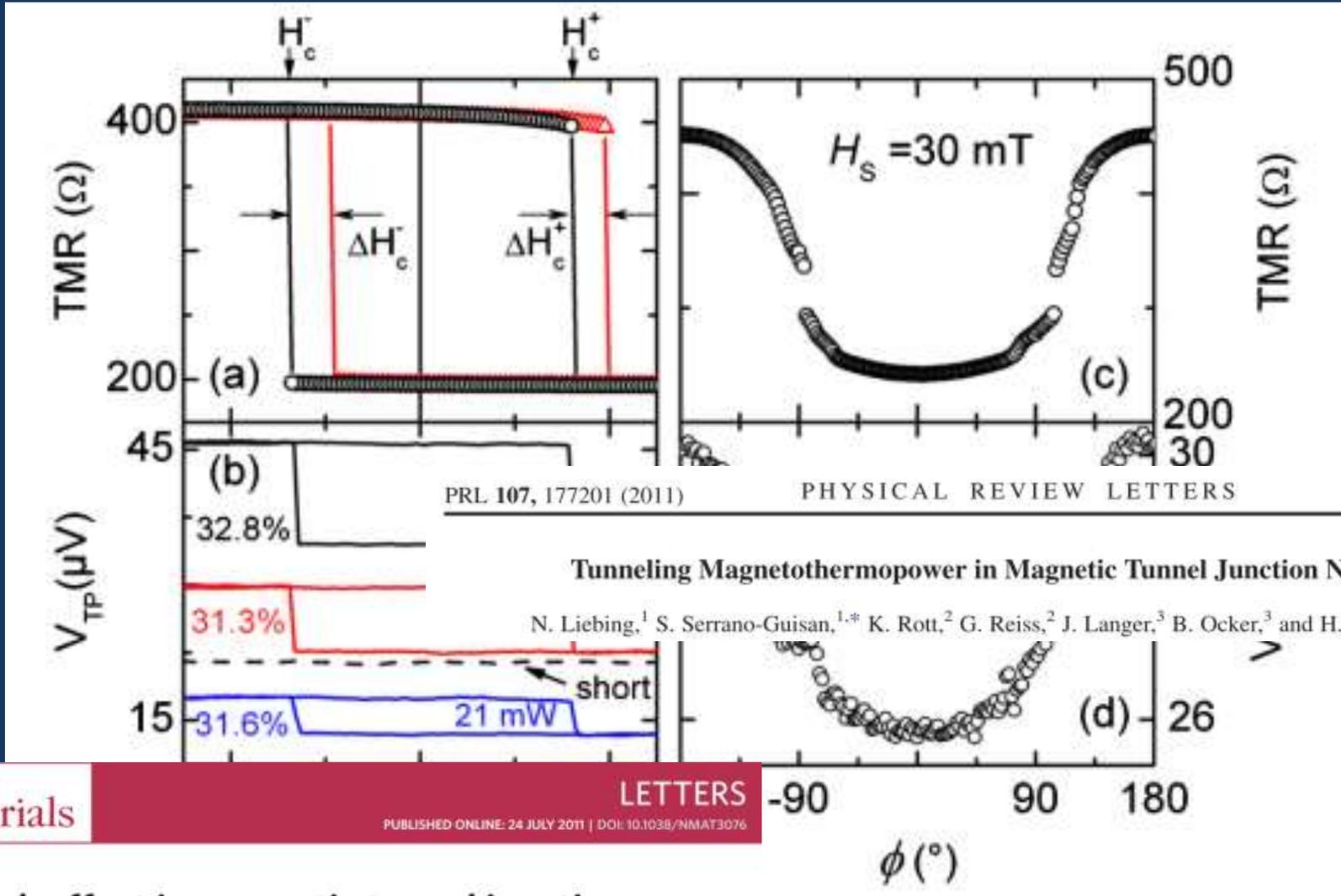
Seebeck coefficient
is caused by
asymmetric DOS at E_F

$$TMTP \text{ or } TMS = \frac{U_{max} - U_{min}}{U_{min}}$$

→ Thermovoltage **U** should depend on magnetization directions

→ Important: **S** ≠ conductivity $g = \frac{e^2}{h} \int T(E)(-\partial_E f(E, \mu, T))dE$

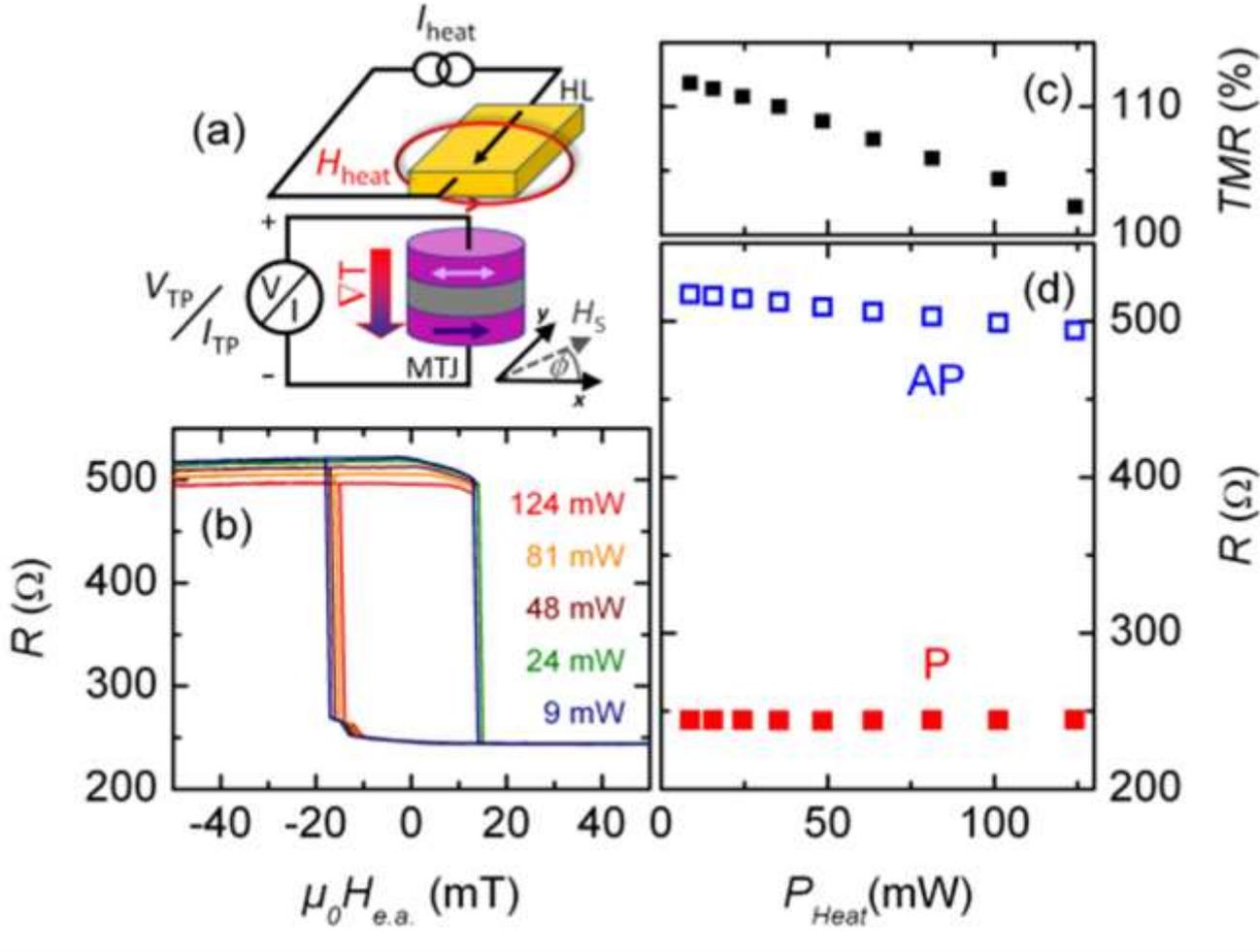




week
21 OCTO

Seebeck effect in magnetic tunnel junctions

Marvin Walter¹, Jakob Walowski¹, Vladyslav Zbarsky¹, Markus Mützenber^{1*}, Markus Schäfers²,
 Daniel Ebke², Günter Reiss², Andy Thomas^{2,3}, Patrick Peretzki⁴, Michael Seibt⁴,
 Jagadeesh S. Moodera⁵, Michael Czerner⁶, Michael Bachmann⁶ and Christian Heiliger⁶



$$I_{Total} = \sigma V_{ext} + \sigma S \nabla T_{MTJ}$$

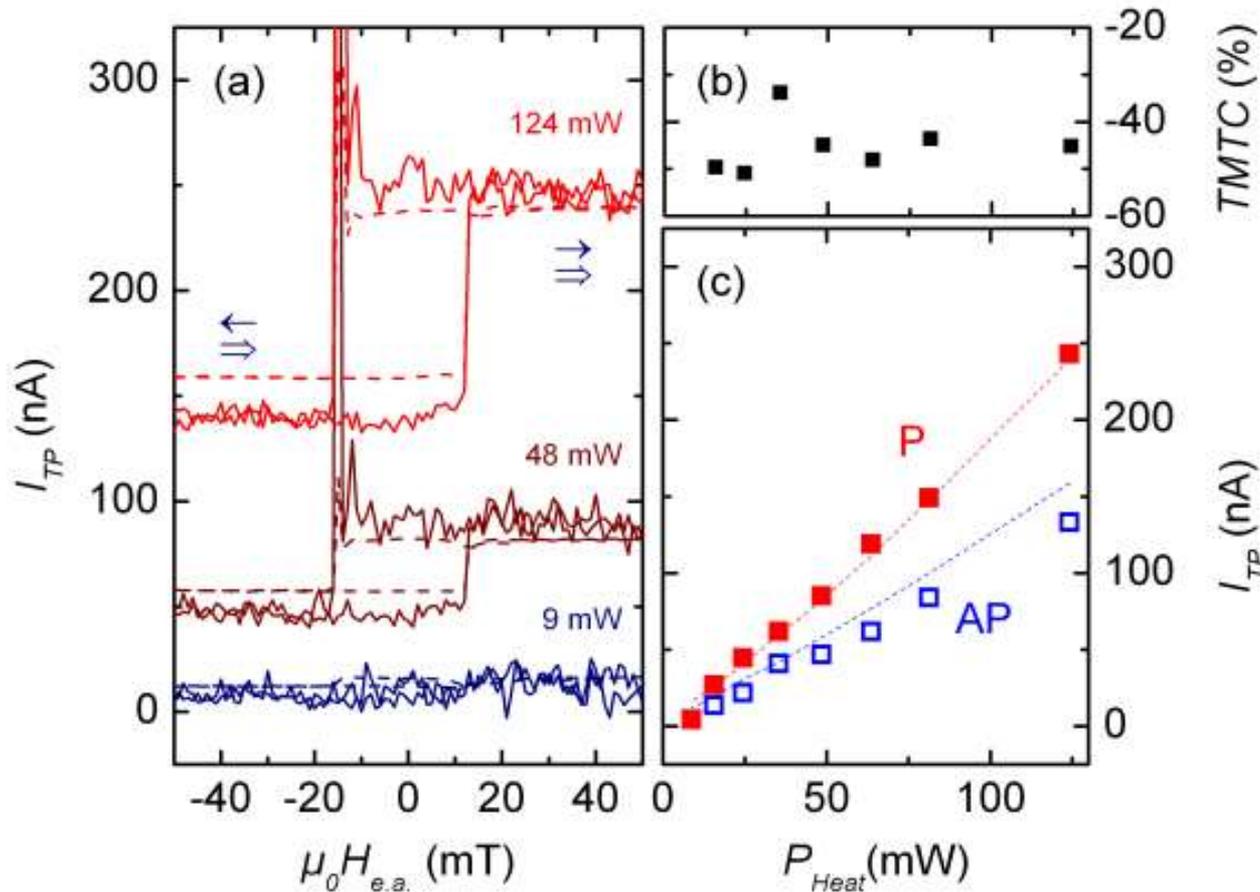
Tunnel-Magneto-Thermocurrent:

$$I_{TP} = \sigma S \nabla T_{MTJ}$$

Note:
 σ changes from P to AP configuration !

Reports: $I_{TP}=0$??





$$I_{Total} = \sigma V_{ext} + \sigma S \nabla T_{MTJ}$$

Tunnel-Magneto-Thermocurrent:

$$I_{TP} = \sigma S \nabla T_{MTJ}$$

Note:
 σ changes from P to AP configuration !

Reports: $I_{TP}=0$??



dashed lines: computed current, solid lines / points: measured values !

Tunneling magneto thermocurrent in CoFeB/MgO/CoFeB based magnetic tunnel junctions

N. Liebing, S. Serrano-Guisan, P. Krzysteczko, K. Rott, G. Reiss et al.

Citation: *Appl. Phys. Lett.* **102**, 242413 (2013); doi: 10.1063/1.4811737

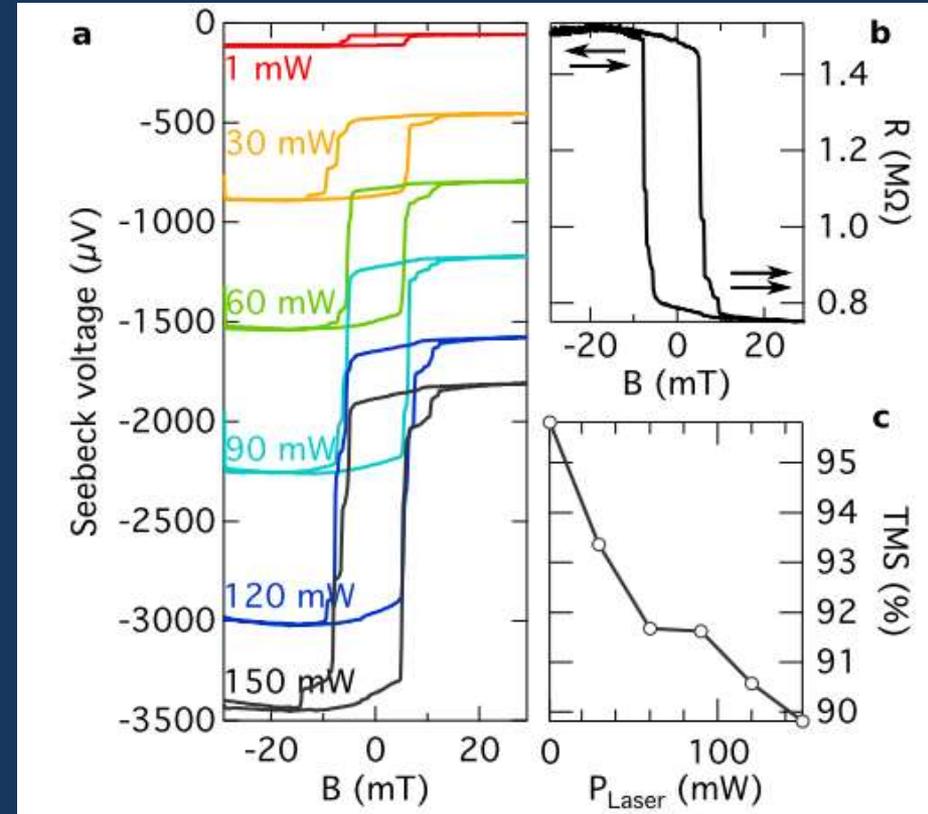
Onsager's relations valid for TMTP ..



Gap in one spin direction should increase not only TMR but also

$$S = \frac{\int T(E)(E - \mu)(-\partial_E f(E, \mu, T))dE}{e T \int T(E)(-\partial_E f(E, \mu, T))dE}$$

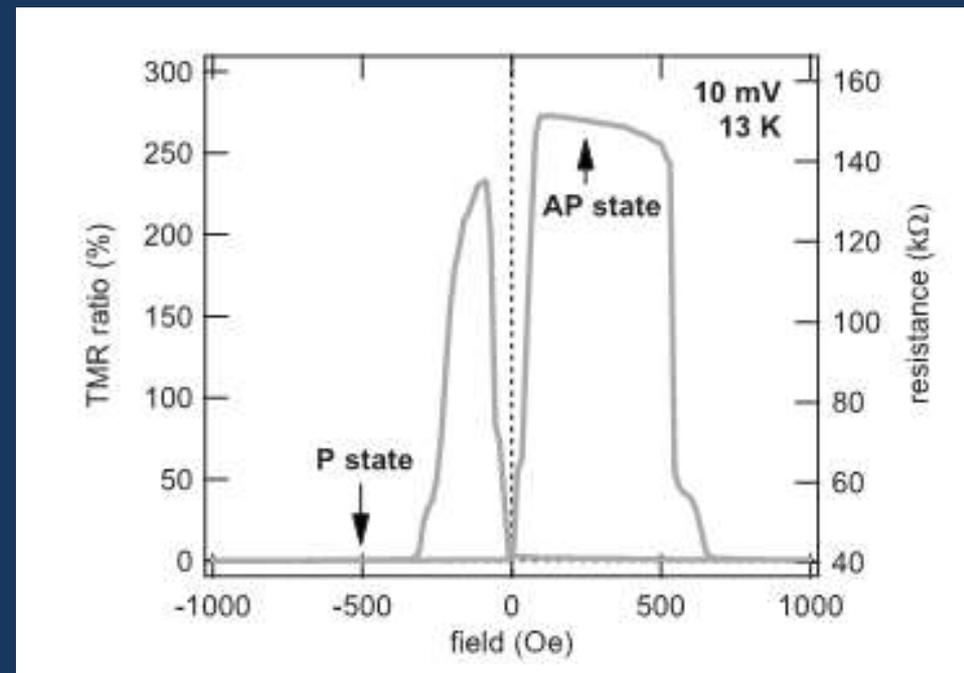
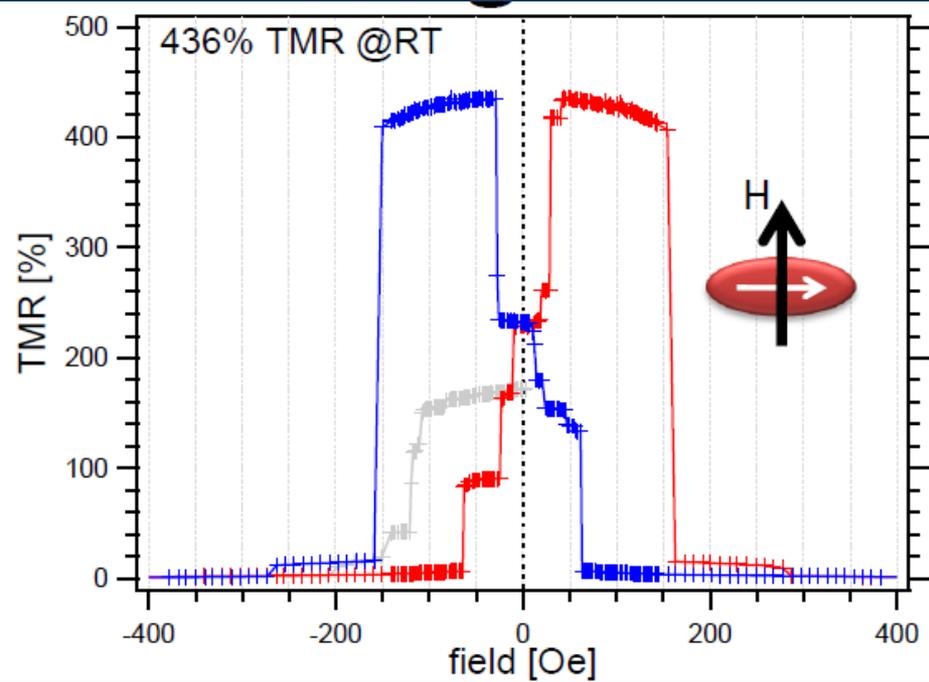
(large asymmetry of DOS at E_F)



a) TMS reaches 90 ... 96 % comparable to TMR (b)

c) Dependence of TMS ratio on applied laser power.

... ongoing experimental and theoretical work



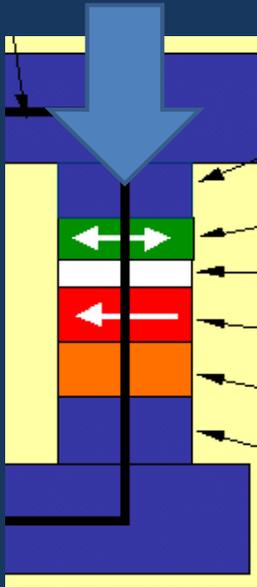
Resistance vs Magnetic Field for:

A CoFeB / MgO / CoFeB
pseudo-spinvalve MTJ

and a Co₂FeAl / MgO / CoFeB structure
Heusler MTJ

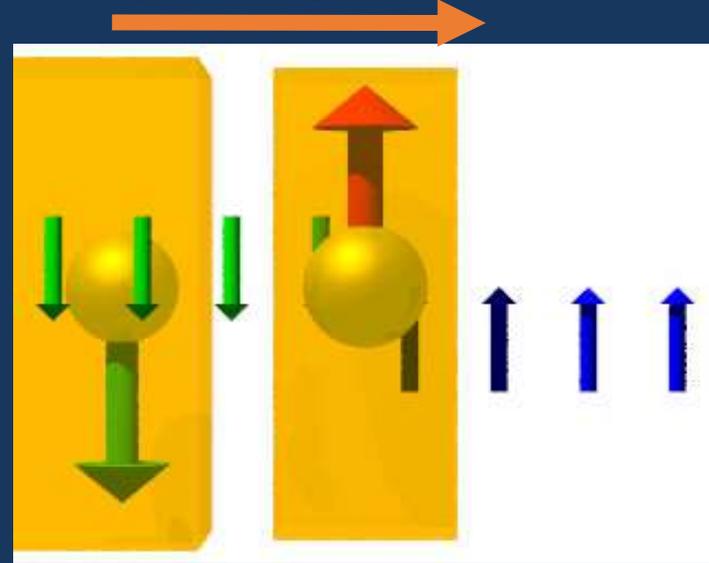
„Normal“ in plane tunnel junctions

Spin Transfer in MTJs



Push high current pulses through tunnel junction

charge & angular momentum



$$\frac{d\mathbf{m}}{dt} = -\gamma(\mathbf{m} \times \mathbf{H}_{\text{eff}}) + \alpha \left(\mathbf{m} \times \frac{d\mathbf{m}}{dt} \right) - T_{J(\text{hot})} \mathbf{m} \times (\mathbf{m} \times \hat{\mathbf{m}}_p),$$

Landau-Lifshitz-Gilbert-Slonczewski equation

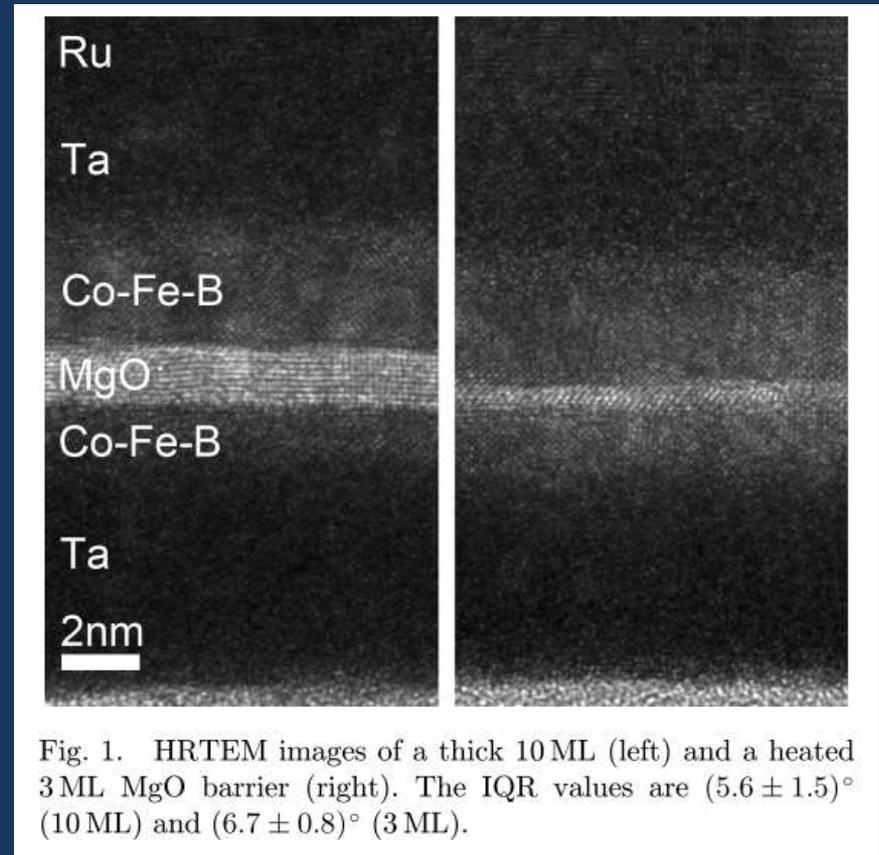
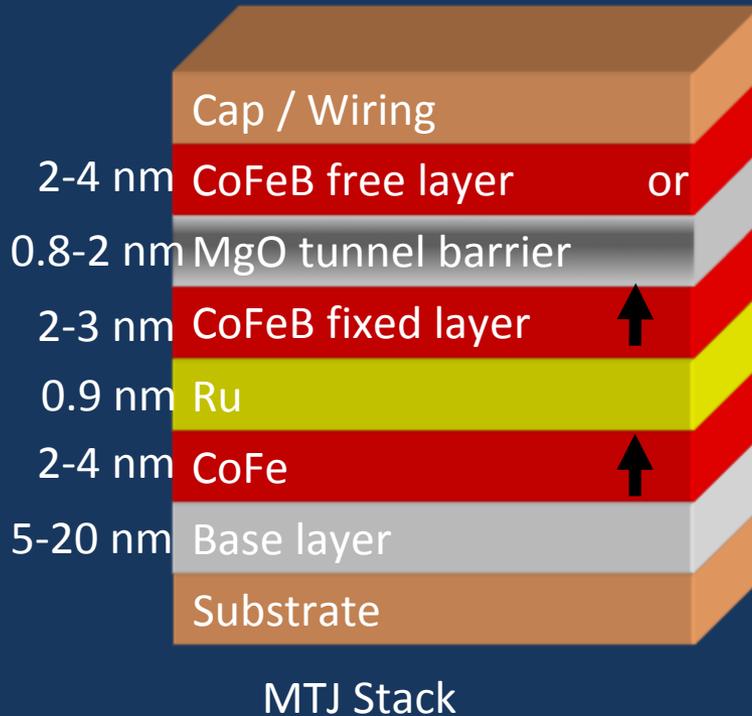
friction torque (damping)

STT – Spin Transfer Torque (antidamping)

→ The spin current switches the device due to transfer of torque

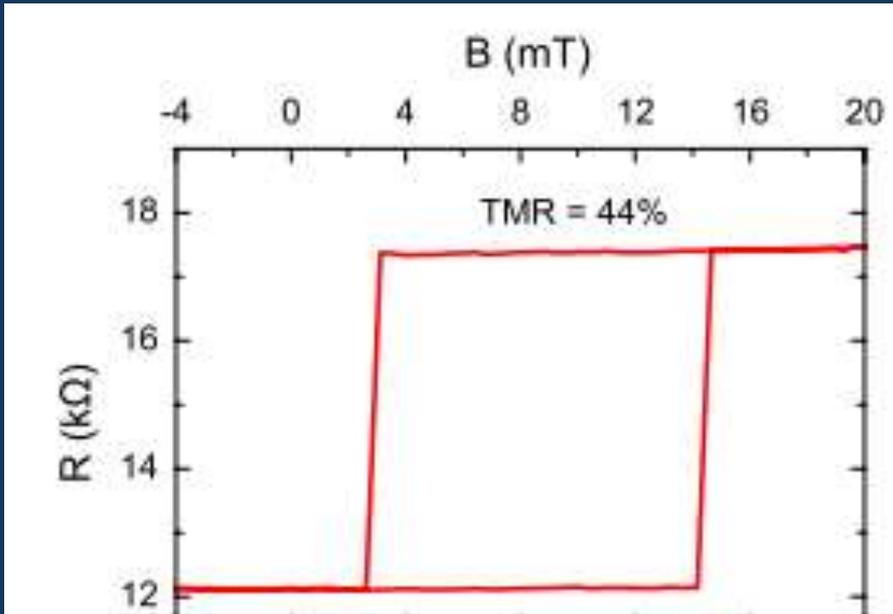
Spintransfer in perpendicular MTJs

The samples:

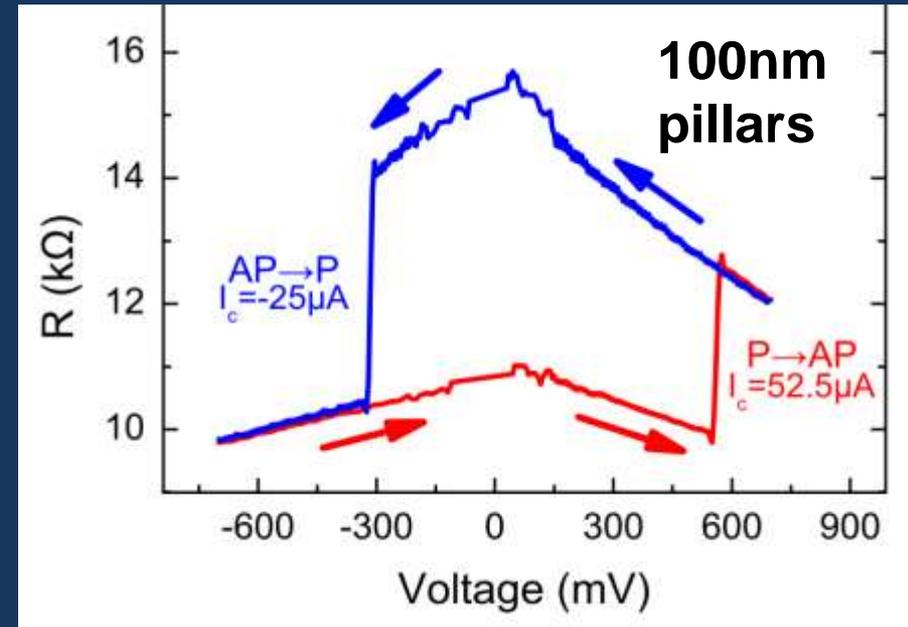


Magnetic Tunnel junctions
with CoFeB (in plane or perpendicular)
and other materials

MgO thickness
down to 3 monolayers



Resistance vs. external magnetic field for perpendicular MTJs
1.0nm CoFeB / 4 ML MgO / 1.2nm CoFeB gives around 40-50% TMR



RV-characteristic with an applied field of 8.6 mT

- average critical current density:

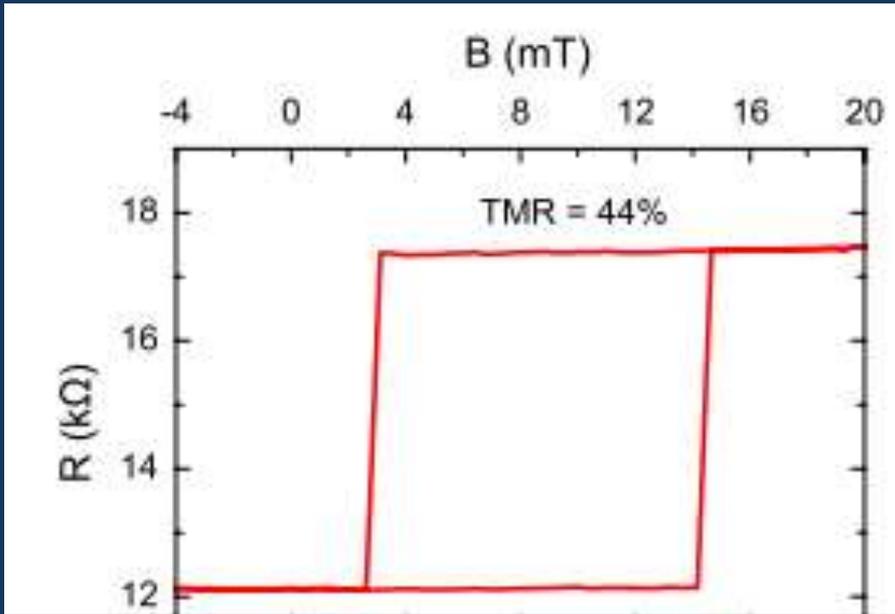
$2 \cdot 10^5 \text{ A/cm}^2$ (!!)

Parameter space for thermal spin-transfer torque

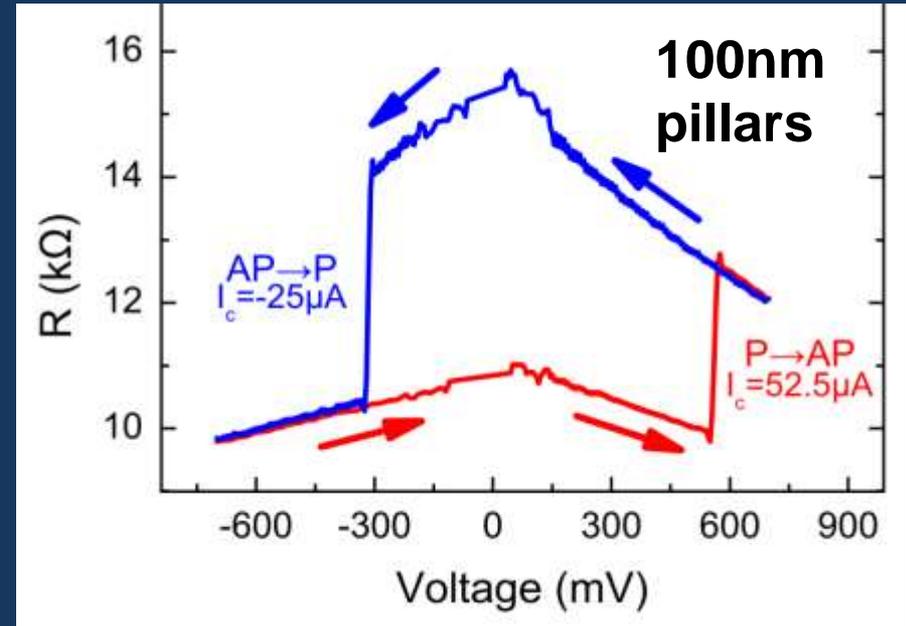
J. C. Leutenantsmeyer,^{1, a)} M. Walter,¹ V. Zbarsky,¹ M. Münzenberg,¹ R. Gareev,² K. Rott,³ A. Thomas,³ G. Reiss,³ P. Peretzki,⁴ H. Schuhmann,⁴ M. Seibt,⁴ M. Czerner,⁵ and C. Heiliger⁵

SPIN

Vol. 3, No. 1 (2013) 1350002 (7 pages)



Resistance vs. external magnetic field for perpendicular MTJs
1.0nm CoFeB / 4 ML MgO / 1.2nm CoFeB gives around 40-50% TMR



RV-characteristic with an applied field of 8.6 mT

- average critical current density:

$2 \cdot 10^5 \text{ A/cm}^2$ (!!)

Parameter space for thermal...

Thermal torque could switch such MTJs if 10K temperature difference across barrier can be realized .. or if J_C is reduced

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Vol. 3, No. 1 (2013) 1350002 (7 pages)

**Latest results:
 J_C can be as small as 10^4 A/cm^2 !!!!**

Free layer:

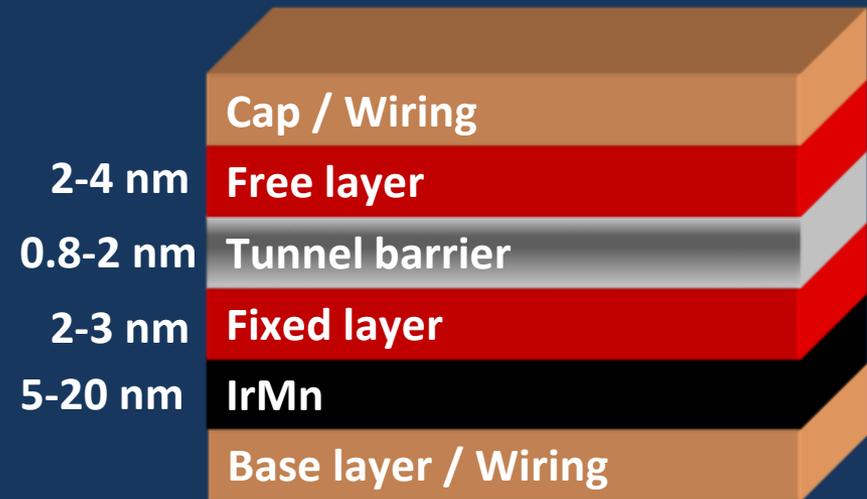
- Low Magnetization
- Small or high damping
- High anisotropy
- Easy to switch
- High spin polarization

Fixed layer

- Moderate magnetization
- Not to switch
- High spin polarization
- Good and affordable exchange bias (perpendicular!)

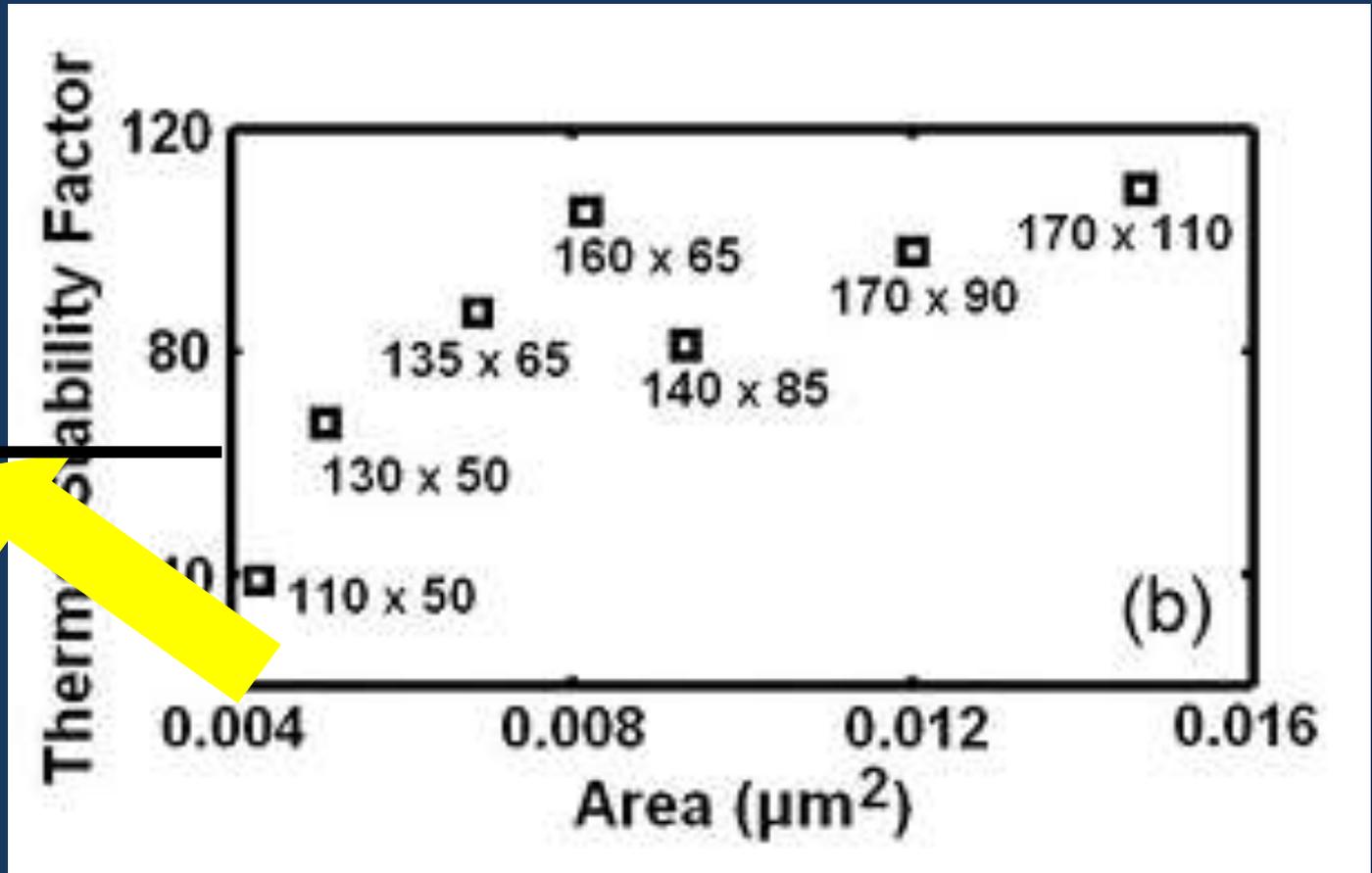
Tunnel barrier

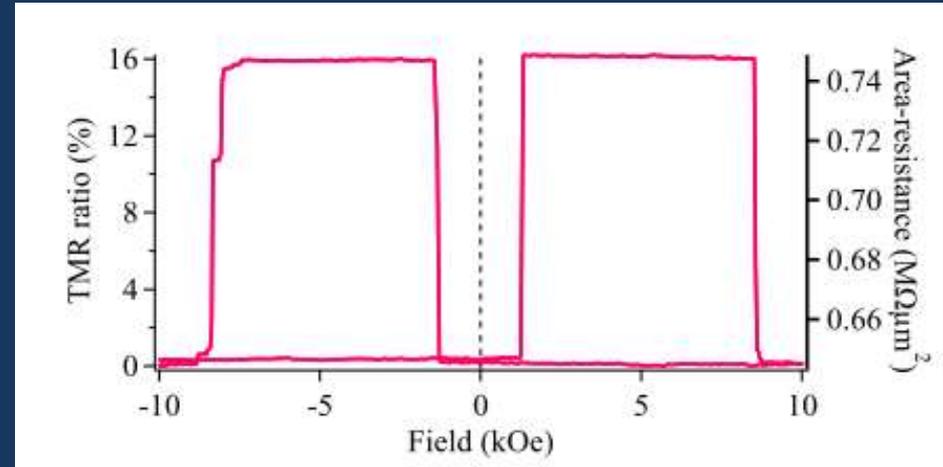
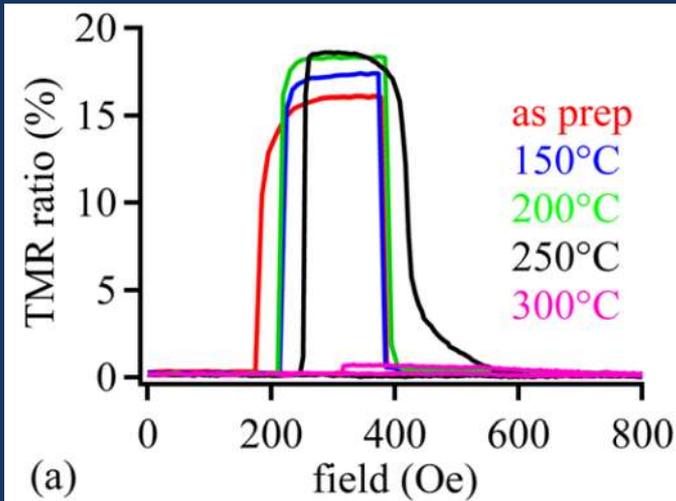
- Good growth on ferromagnet
- Spin filtering
- Good substrate for ferromagnet

**MTJ Stack**

Thermal stability $KV / kT > 60$ for 10-years data retention:
CoFeB on MgO possibly not good enough

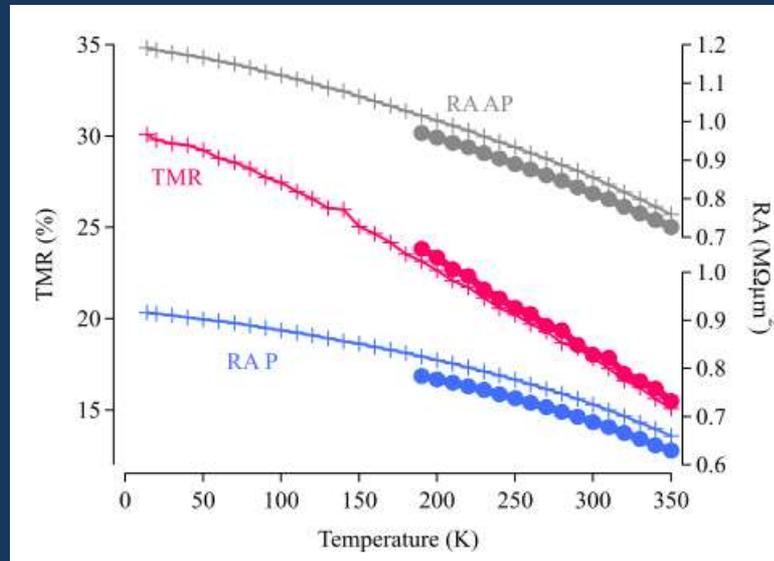
Goal:
 $10 \times 10 \text{ nm}^2 =$
 $0.001 \mu\text{m}^2$





TMR loops of multilayers CoPt
.../(Co_{0.6}/Pt_{1.8})₄ /Co_{0.7}/ Mg_{0.5}/ MgO_{2.1}
/ (Co_{0.7}/Pt_{1.8})₂ /... at 300 K

Major loop of alloys .../(CoFe)₇₉Tb₂₁ 30nm /
CoFeB 1nm /Mg 0.5nm /MgO 2.1nm /
CoFeB 1nm / (CoFe)₇₉Tb₂₁ 10nm /... at 360 K



Both show similar
good temperature
dependence

But:
Large damping
So far low TMR

Zoë Kugler, J.-P. Grote, V. Drewello,
O. Schebaum, GR,
J. Appl. Phys. 111,
07C703 (2012)

.. candidate systems:

The Heusler-class $Mn_{3-x}Ga$ and $Mn_{2-x}Co_{1-y}Ga$

Perp.

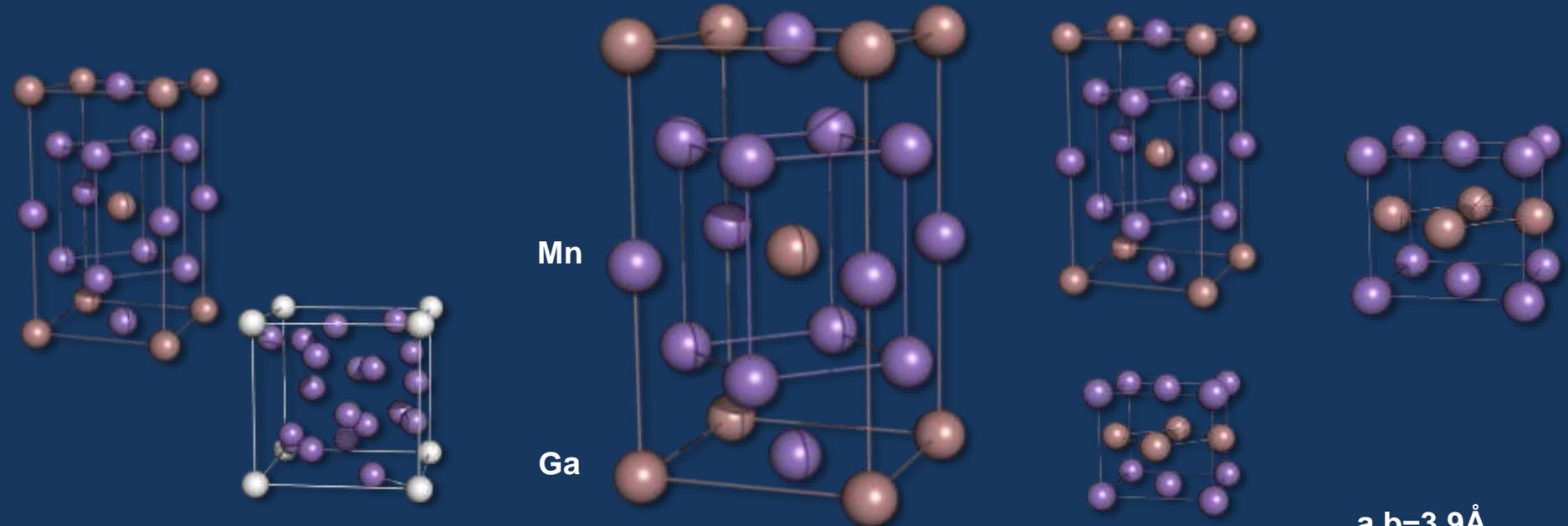
Perp.

$DO_{22} + \beta\text{-Mn}$

tetragonal DO_{22}

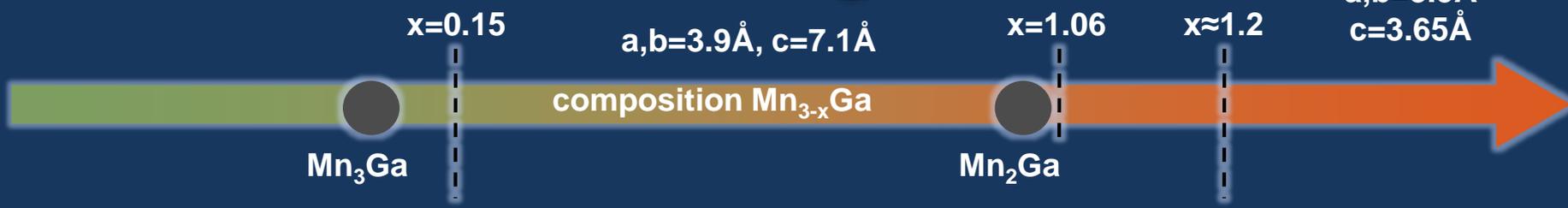
$L1_0 + DO_{22}$

$L1_0$



Mn

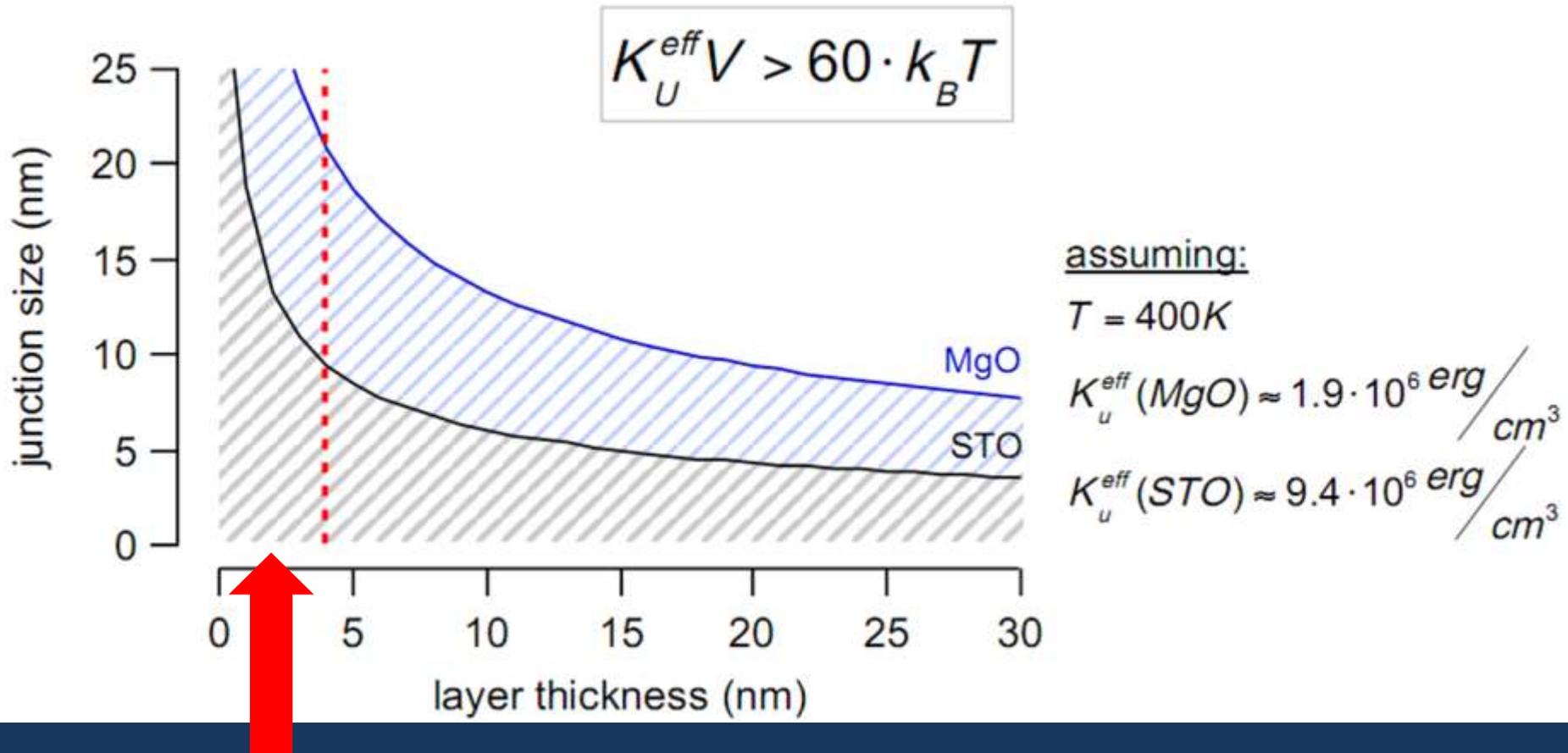
Ga



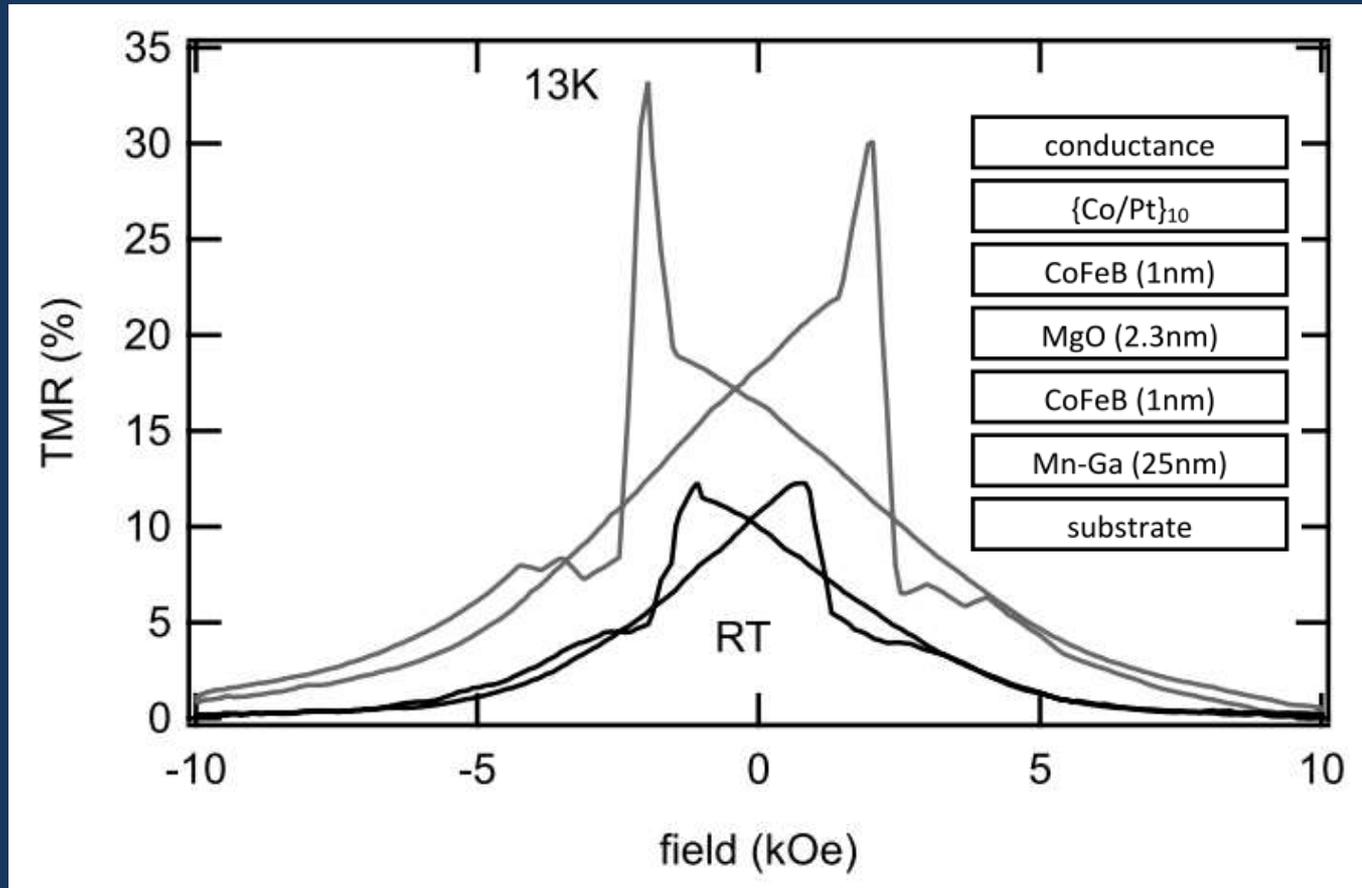
$a, b = 3.9 \text{ \AA}, c = 7.1 \text{ \AA}$

$a, b = 3.9 \text{ \AA}$
 $c = 3.65 \text{ \AA}$

First results on $\text{Mn}_{2.6}\text{Ga}$: Very strong perpendicular anisotropy, low magnetization

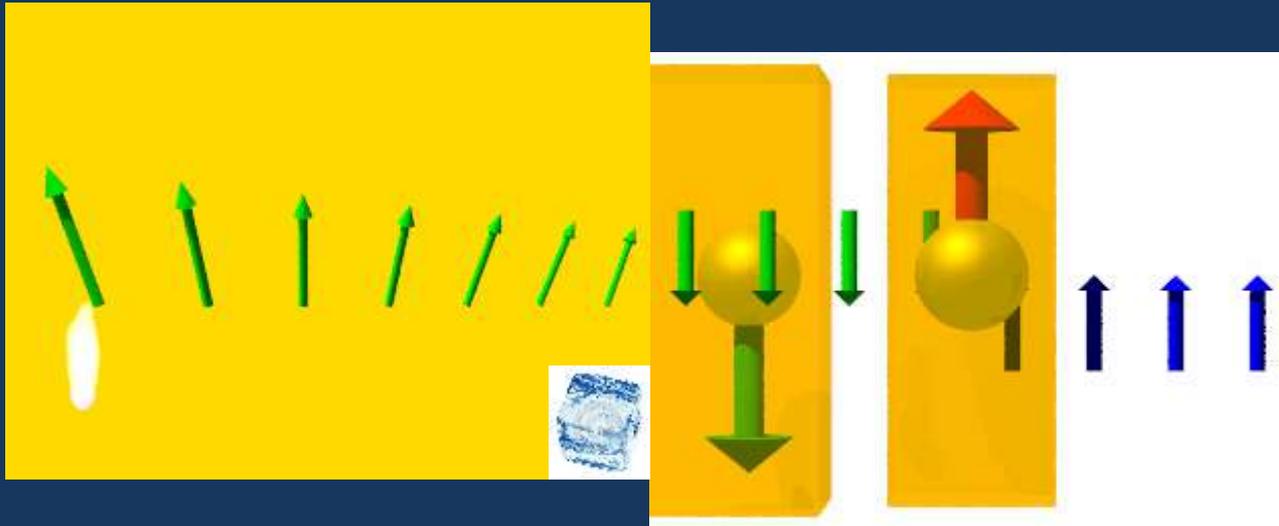


Could work down to 5nm feature size !

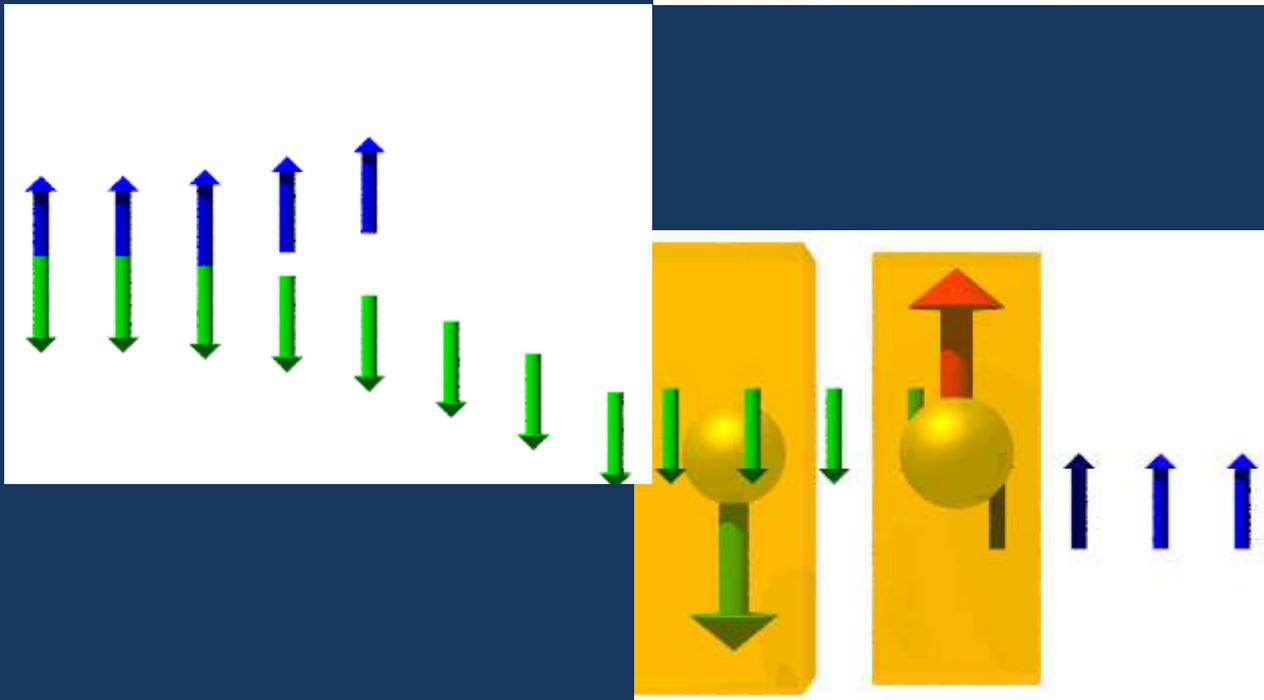


Material gives TMR, but up to now only with CoFeB interlayer and not yet completely antiparallel aligned .. further work on the way

- ▶ **Thermally driven spin currents in insulators**
→ LSSE (+ ANE, PNE)
- ▶ **Thermally driven spin currents in MTJs**
→ TMTP, TMS
- ▶ **Spin transfer and torque in magnetic tunnel junctions**
→ STT (+oscillations)



Thermal
STT switching ?



STT switching
by SO-interaction

-- Spin-Orbit-
Torque ?

Thanks

All coworkers in Bielefeld



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Ch. Klewe

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BMBF

NRW (Northrhine Westfalia)

European Commission

Thyssen Krupp Foundation

Humboldt Foundation

.. and you for
listening !

Round Robin Experiment for Spin Seebeck Effects within EMRP-Project:
contact H.W. Schumacher

Samples / Lithography: Center for Spinelectronic Materials and Devices,
<http://www.physik.uni-bielefeld.de/experi/d2/research/CSMD.html>
contact: Speaker

